TEXAS INSTRUMENTS

ISOW7840, ISOW7841
ISOW7842, ISOW7843, ISOW7844

ZHCSG29F – MARCH 2017 – REVISED MARCH 2019

ISOW784x 具有集成式高效低辐射直流/直流转换器的高性能、5000V_{RMS} 四通道增强型数字隔离器

1 特性

- 100Mbps 数据速率
- 稳健可靠的隔离栅：中添加了项目符号“稳健可靠的隔离栅”
  - 在 1kV_{RMS} 工作电压下，预计使用寿命超过 100 年中添加了项目符号“在 1kV_{RMS} 工作电压下，预计使用寿命超过 100 年”
  - 高达 5000V 的 $_{RMS}$ 隔离额定值中添加了项目符号“高达 5000V 的 $_{RMS}$ 隔离额定值”
  - 高达 10kV_{PK} 浪涌能力中添加了项目符号“高达 10kV_{PK} 的浪涌能力”
  - ±100 kV/µs 最低 CMTI
- 集成高效直流/直流转换器与片上变压器
- 3V 至 5.5V 宽电源电压范围
- 5V 或 3.3V 稳压输出
- 高达 0.65W 的输出功率
- 5V 至 5V；5V 至 3.3V：可用负载电流 ≥ 130mA
- 3.3V 至 3.3V：可用负载电流 ≥ 75mA
- 软启动可限制浪涌电流
- 过载和短路保护
- 热关断
- 默认输出：*高电平*和*低电平*选项
- 低传播延迟：电源为 5V 时的典型值为 13ns
- 优异的电磁兼容性 (EMC)
  - 系统级 ESD、EFT 和浪涌抗扰性
  - ±8kV IEC 61000-4-2 跨隔离栅接触放电保护中添加了项目符号“±8kV IEC 61000-4-2 跨隔离栅接触放电保护”
  - 低辐射
- 16 引脚宽体 SOIC 封装
- 扩展温度范围：-40°C 至 +125°C
- 安全相关认证：
  - 符合 DIN V VDE V 0884-11:2017-01 标准的 7071V_{PK} 增强型隔离
  - UL 1577 标准下，长达 1 分钟的 5000V_{RMS} 隔离
  - 获得 CSA 认证，符合 IEC 60950-1、IEC 62368-1 和 IEC 60601-1 终端设备标准
  - 符合 GB4943.1-2011 的 CQC 认证
  - 符合 EN 60950-1 和 EN 61010-1 的 TUV 认证

2 应用

- 工业自动化
- 电机控制
- 电网基础设施
- 医疗设备
- 测试和测量

3 说明

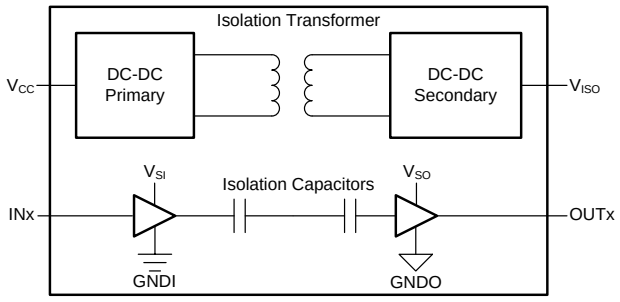
ISOW784x 是一系列具有集成式高效电源转换器的高性能四通道增强型数字隔离器。集成式直流/直流转换器高效运行，提供最高可达 650mW 的隔离式电源，可配置为各种输入和输出电压配置。因此，空间受限的隔离设计凭借该器件无需单独使用隔离式电源。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
ISOW7840 ISOW7841 ISOW7842 ISOW7843 ISOW7844	SOIC (16)	10.30mm x 7.50mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化原理图



V_{CC} 是以 GND1 为基准的主电源电压。V_{ISO} 是以 GND2 为基准的隔离电源电压。

V_{SI} 和 V_{SO} 可为 V_{CC} 或 V_{ISO}，具体取决于通道方向。

V_{SI} 是以 GNDI 为基准的输入侧电源电压，而 V_{SO} 是以 GNDO 为基准的输出侧电源电压。

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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision E (November 2017) to Revision F **Page**

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- 更新了简化原理图，以便显示信号隔离通道的两个串联隔离电容器，而不是单个电容器 ... 1
- Added "Contact discharge per IEC 61000-4-2; Isolation barrier withstand test" specification of ±8000 in ESD Ratings table ... 7
- Added table note "IEC ESD strike is applied across the barrier with all pins on each side tied together creating a two-terminal device" to ESD Ratings table ... 7
- Deleted "T_J or Junction temperature" parameter from Recommended Operating Conditions table as it is already specified in Absolute Maximum Ratings table ... 7
- Added "see 图 42" to TEST CONDITIONS of V_{IOWM} specification ... 9
- Added the following note to 图 33: "Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations" ... 30
- Added the following note to 图 38: "Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations" ... 36

修订历史记录 **(**接下页**)**

- Added the following text to Design Requirements: "Optional 100 µF decoupling capacitor can be added between V_{CC} and GND1 pins; refer to Power Supply Recommendations for more details 37
- Added the following note to 图 39: "Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations" 37
- Added *Insulation Lifetime* sub-section under Application Curve section 38
- Added text to Power Supply Recommendations section to emphasise that input decoupling capacitor should be larger than output capacitor by at least 100 µF 39
- Added the following note to 图 43: "Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations" 41

Changes from Revision D (November 2017) to Revision E **Page**

- 已更改 ISOW7843 器件从“*预览*”更改为“*生产数据*” 5
- Added the ISOW7843 current parameters to each *Supply Current Characteristics* table 13
- 已添加 the supply current versus data rate graphs for the ISOW7843 in the *Typical Characteristics* section 26

Changes from Revision C (October 2017) to Revision D **Page**

- 已更改 ISOW7840 器件从“*预览*”更改为“*生产数据*” 5
- Added the ISOW7840 current parameters to each *Supply Current Characteristics* table 12
- Changed I_{ISO} to I_{LOAD} and the value of wave clock input from 0.5, 5, and 50 MHz to 1, 10, and 100 Mbps in the test conditions for the ISOW7841 current parameters in each *Supply Current Characteristics* table 12
- Deleted *no external* I_{LOAD} test condition for the current available to isolated supply parameter for the ISOW7842 and ISOW7844 devices in each *Supply Current Characteristics* table 13
- 已更改 the labels of the curves in the *Thermal Derating Curve for Safety Limiting Current per VDE* 24
- 已添加 the supply current versus data rate graphs for the ISOW7840 in the *Typical Characteristics* section 25
- 已更改 the ground symbols for the input schematic for devices with F suffix and the SEL pin in the *Device I/O Schematics* figure 35

Changes from Revision B (June 2017) to Revision C **Page**

- 更改了*安全相关认证* 引脚 列表 1
- Changed header row From: DIN V VDE 0884-10 (VDE V 0884-10): 2016-12 To: DIN V VDE 0884-11:2017-01 in the *Insulation Specifications* 9
- Changed V_{IOSM} test conditions in *Insulation Specifications* 9
- Changed $V_{ISO(UL)}$ test conditions in *Insulation Specifications* 9
- Changed the *Safety-Related Certifications* table 10
- Changed Note 1 of the *Safety Limiting Values* table 10
- Added the ISOW7842 current parameters to each *Supply Current* table 13
- 已添加 the supply current versus data rate graphs for the ISOW7842 in the *Typical Characteristics* section 26

Changes from Revision A (March 2017) to Revision B **Page**

- Added the ISOW7844 current parameters to each *Supply Current* table 14

Changes from Original (March 2017) to Revision A **Page**

- Changed the maximum propagation delay time and the typical and maximum values for pulse width distortion in all *Switching Characteristics* tables 23
- Changed the maximum limit for output signal rise and fall times from 3 to 4 ns in the *Switching Characteristics—5-V Input, 3.3-V Output* table 23

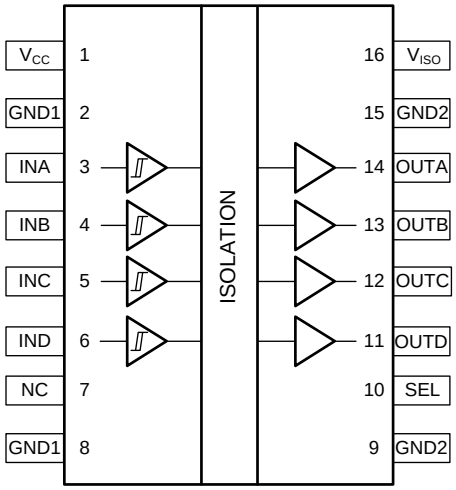
5 说明 （续）

ISOW784x 系列器件可提供高电磁抗扰度和低辐射。该信号隔离通道具有逻辑输入和输出缓冲器，采用双电容二氧化硅 (SiO_2) 绝缘栅进行隔离，而电源隔离则采用片上变压器，采用薄膜聚合物作为绝缘材料进行隔离。 提供多种正向和反向通道配置。 如果输入信号丢失，ISOW784x 器件不带 F 后缀的 默认输出高电平，而带有后缀 F 后缀的器件默认输出低电平（请参阅 *表 1*）。

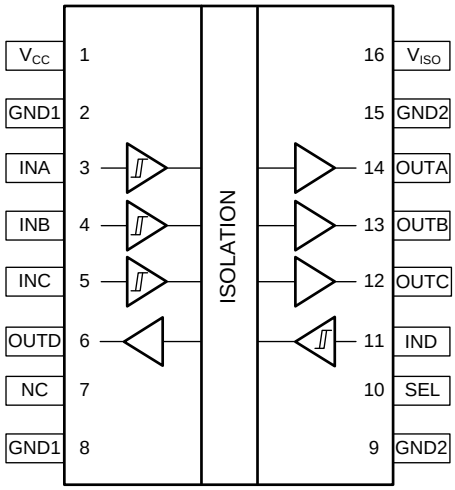
这些器件有助于防止数据总线（例如，RS-485、RS-232 和 CAN）或者其他电路上的噪声电流进入本地接地以及干扰或损坏敏感电路。凭借创新型芯片设计和布线技术，该器件的电磁兼容性得到了显著增强，可缓解系统级 ESD、EFT 和浪涌问题并符合辐射标准。电源转换器效率较高，允许在较高的环境温度下工作。器件采用 16 引脚 SOIC 宽体 (SOIC-WB) DWE 封装。

6 Pin Configuration and Functions

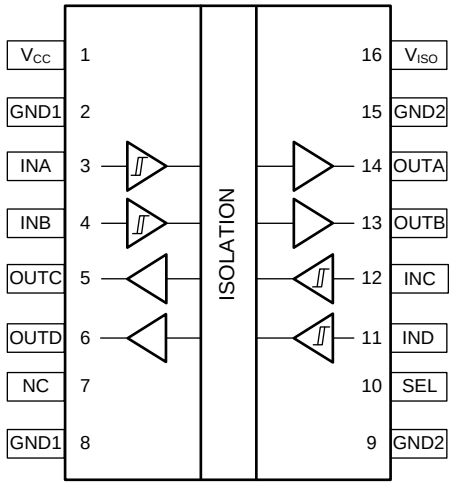
ISOW7840 DWE Package
16-Pin SOIC-WB
Top View



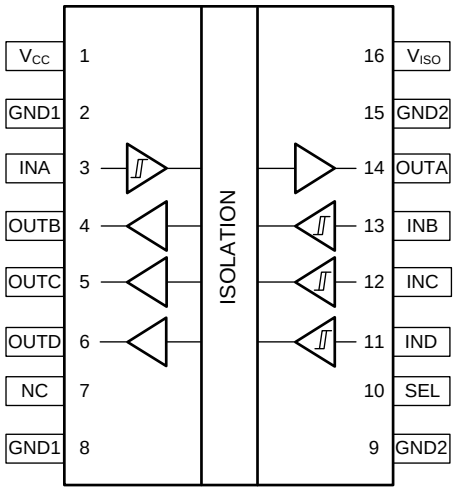
ISOW7841 DWE Package
16-Pin SOIC-WB
Top View



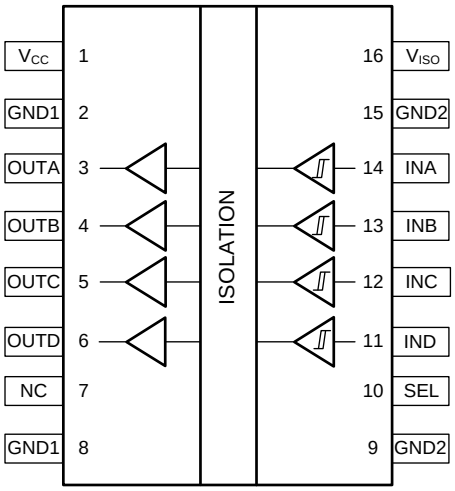
ISOW7842 DWE Package
16-Pin SOIC-WB
Top View



ISOW7843 DWE Package
16-Pin SOIC-WB
Top View



ISOW7844 DWE Package
16-Pin SOIC-WB
Top View



Pin Functions

PIN						I/O	DESCRIPTION
NAME	NO.						
	ISOW7840	ISOW7841	ISOW7842	ISOW7843	ISOW7844		
GND1	2, 8	2, 8	2, 8	2, 8	2, 8	—	Ground connection for V_{CC}
GND2	9, 15	9, 15	9, 15	9, 15	9, 15	—	Ground connection for V_{ISO}
INA	3	3	3	3	14	I	Input channel A
INB	4	4	4	13	13	I	Input channel B
INC	5	5	12	12	12	I	Input channel C
IND	6	11	11	11	11	I	Input channel D
NC	7	7	7	7	7	—	Not connected
OUTA	14	14	14	14	3	O	Output channel A
OUTB	13	13	13	4	4	O	Output channel B
OUTC	12	12	5	5	5	O	Output channel C
OUTD	11	6	6	6	6	O	Output channel D
SEL	10	10	10	10	10	I	V_{ISO} selection pin. V_{ISO} = 5 V when SEL shorted to V_{ISO}. V_{ISO} = 3.3 V, when SEL shorted to GND2 or when left floating. For more information see the *Device Functional Modes*.
V_{CC}	1	1	1	1	1	—	Supply voltage
V_{ISO}	16	16	16	16	16	—	Isolated supply voltage determined by SEL pin

7 Specifications

7.1 Absolute Maximum Ratings

See (1)(2)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	–0.5	6	V
V_{ISO}	Isolated supply voltage	–0.5	6	V
V_{IO}	Voltage at INx, OUTx, SEL pins	–0.5	V_{CC} + 0.5, V_{ISO} + 0.5 (3)	V
I_O	Maximum output current through data channels	–15	15	mA
T_J	Junction temperature		150	°C
T_{stg}	Storage temperature	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values except differential I/O bus voltages are with respect to the local ground pin (GND1 or GND2) and are peak voltage values.
(3) This value depends on whether the pin is located on the V_{CC} or V_{ISO} side. The maximum voltage at the I/O pins should not exceed 6 V.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	
		Contact discharge per IEC 61000-4-2; Isolation barrier withstand test (3)	±8000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.
(3) IEC ESD strike is applied across the barrier with all pins on each side tied together creating a two-terminal device.

7.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		3		5.5	V
I_{OH}	High level output current (2)	V_{SO} (1) = 5 V	–4			mA
		V_{SO} = 3.3 V	–2			
I_{OL}	Low level output current (2)	V_{SO} = 5 V			4	mA
		V_{SO} = 3.3 V			2	
V_{IH}	High-level input voltage		0.7 × V_{SI}		V_{SI}	V
V_{IL}	Low-level input voltage		0		0.3 × V_{SI}	V
DR	Data rate				100	Mbps
T_A	Ambient temperature		–40		125	°C

(1) V_{SI} is the input side supply, V_{SO} is the output side supply
(2) This current is for data output channel.

7.4 Thermal Information

THERMAL METRIC(1)		ISOW784x DWE (SOIC) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	56.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	15.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	28.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	2.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	28.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

7.5 Power Ratings

V_{CC} = 5.5 V, I_{ISO} = 110 mA, T_J = 150°C, T_A ≤ 80°C, C_L = 15 pF, input a 50-MHz 50% duty-cycle square wave

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D	Maximum power dissipation (both sides)				1.02	W
P_{D1}	Maximum power dissipation (side-1)				0.51	W
P_{D2}	Maximum power dissipation (side-2)				0.51	W

7.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External clearance(1)	Shortest terminal-to-terminal distance through air	>8	mm
CPG	External creepage(1)	Shortest terminal-to-terminal distance across the package surface	>8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance – capacitive signal isolation)	> 21	µm
		Minimum internal gap (internal clearance – transformer power isolation)	>120	
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	> 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 300 V_{RMS}	I-IV	
		Rated mains voltage ≤ 600 V_{RMS}	I-IV	
		Rated mains voltage ≤ 1000 V_{RMS}	I-III	
DIN V VDE 0884-11:2017-01(2)				
V_{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1414	V_{PK}
V_{IOWM}	Maximum working isolation voltage	AC voltage; Time dependent dielectric breakdown (TDDB) Test; See 图 42	1000	V_{RMS}
		DC voltage	1414	V_{DC}
V_{IOTM}	Maximum transient isolation voltage	$V_{TEST} = V_{IOTM}$; t = 60 s (qualification); $V_{TEST} = 1.2 \times V_{IOTM}$; t = 1 s (100% production)	7071	V_{PK}
V_{IOSM}	Maximum surge isolation voltage(3)	Test method per IEC 62368-1, 1.2/50 µs waveform, $V_{TEST} = 1.6 \times V_{IOSM} = 10000\ V_{PK}$(qualification)	6250	V_{PK}
q_{pd}	Apparent charge(4)	Method a, after input/output safety test subgroup 2/3, $V_{ini} = V_{IOTM}$, t_{ini} = 60 s; $V_{pd(m)} = 1.2 \times V_{IORM}$, t_m = 10 s	≤ 5	pC
		Method a, after environmental tests subgroup 1, $V_{ini} = V_{IOTM}$, t_{ini} = 60 s; $V_{pd(m)} = 1.6 \times V_{IORM}$, t_m = 10 s	≤ 5	
		Method b1, at routine test (100% production) and preconditioning (type test), $V_{ini} = 1.2 \times V_{IOTM}$, t_{ini} = 1 s; $V_{pd(m)} = 1.875 \times V_{IORM}$, t_m = 1 s	≤ 5	
C_{IO}	Barrier capacitance, input to output(5)	V_{IO} = 0.4 × sin (2πft), f = 1 MHz	~3.5	pF
R_{IO}	Insulation resistance(5)	V_{IO} = 500 V, T_A = 25°C	$> 10^{12}$	Ω
		V_{IO} = 500 V, 100°C ≤ T_A ≤ 125°C	$> 10^{11}$	
		V_{IO} = 500 V, T_S = 150°C	$> 10^{9}$	
	Pollution degree		2	
	Climatic category		40/125/21	
UL 1577				
$V_{ISO(UL)}$	Withstand isolation voltage	$V_{TEST} = V_{ISO(UL)}$= 5000 V_{RMS}, t = 60 s (qualification), $V_{TEST} = 1.2 \times V_{ISO(UL)}$ = 6000 V_{RMS}, t = 1 s (100% production)	5000	V_{RMS}

(1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.
(2) This coupler is suitable for safe electrical insulation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
(3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
(4) Apparent charge is electrical discharge caused by a partial discharge (pd).
(5) All pins on each side of the barrier tied together creating a two-terminal device.

7.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV
Certified according to DIN V VDE V 0884-11:2017-01	Certified according to IEC 60950-1, IEC 62368-1, and IEC 60601-1	Recognized under UL 1577 Component Recognition Program	Certified according to GB 4943.1-2011	Certified according to EN 61010-1:2010 and EN 60950- 1:2006/A2:2013
Reinforced insulation; Maximum transient isolation voltage, 7071 V_{PK}; Maximum repetitive peak isolation voltage, 1414 V_{PK}; Maximum surge isolation voltage, 6250 V_{PK}	Reinforced insulation per CSA 60950-1-07+A1+A2, IEC 60950-1 2nd Ed.+A1+A2, CSA 62368-1-14 and IEC 62368-1 2nd Ed., 800 V_{RMS} maximum working voltage (pollution degree 2, material group I); 2 MOPP (Means of Patient Protection) per CSA 60601-1:14 and IEC 60601-1 Ed. 3+A1, 250 V_{RMS} maximum working voltage; Temperature rating is 90°C for reinforced insulation and 125°C for basic insulation; see certificate for details.	Single protection, 5000 V_{RMS}	Reinforced Insulation, Altitude ≤ 5000 m, Tropical Climate, 700 V_{RMS} maximum working voltage;	5000 V_{RMS} Reinforced insulation per EN 61010-1:2010 up to working voltage of 600 V_{RMS}; 5000 V_{RMS} Reinforced insulation per EN 60950-1:2006/A2:2013 up to working voltage of 800 V_{RMS}
Certificate number: 40040142	Master contract number: 220991	File number: E181974	Certificate number: CQC15001121716	Client ID number: 77311

7.8 Safety Limiting Values

Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S	Safety input, output, or supply current(1)	$R_{\theta JA}$ = 56.8°C/W, V_I = 5.5 V, T_J = 150°C, T_A = 25°C, see 图 1			400	mA
		$R_{\theta JA}$ = 56.8°C/W, V_I = 3.6 V, T_J = 150°C, T_A = 25°C, see 图 1			611	
P_S	Safety input, output, or total power(1)	$R_{\theta JA}$ = 56.8°C/W, T_J = 150°C, T_A = 25°C, see 图 2			2200	mW
T_S	Maximum safety temperature(1)				150	°C

(1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A.
The junction-to-air thermal resistance, $R_{\theta JA}$, in the *Thermal Information* table is that of a device installed on a high-K test board for leaded surface-mount packages. Use the following equations to calculate the value for each parameter:
$T_J = T_A + R_{\theta JA} \times P$, where P is the power dissipated in the device.
$T_{J(max)} = T_S = T_A + R_{\theta JA} \times P_S$, where $T_{J(max)}$ is the maximum allowed junction temperature.
$P_S = I_S \times V_I$, where V_I is the maximum input voltage.

7.9 Electrical Characteristics—5-V Input, 5-V Output

V_{CC} = 5 V ±10%, SEL shorted to V_{ISO} (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{ISO}	Isolated supply voltage	External I_{ISO} = 0 to 50 mA	4.75	5.07	5.43	V
		External I_{ISO} = 0 to 130 mA	4.5	5.07	5.43	
$V_{ISO(LINE)}$	DC line regulation	I_{ISO} = 50 mA, V_{CC} = 4.5 V to 5.5 V		2		mV/V
$V_{ISO(LOAD)}$	DC load regulation	I_{ISO} = 0 to 130 mA		1%		
EFF	Efficiency at maximum load current	I_{ISO} = 130 mA, C_{LOAD} = 0.1 µF || 10 µF; V_I = V_{SI} (ISOW784x); V_I = 0 V (ISOW784x with F suffix)		53%		
$V_{CC+(UVLO)}$	Positive-going UVLO threshold on V_{CC}, V_{ISO}				2.7	V
$V_{CC–(UVLO)}$	Negative-going UVLO threshold on V_{CC}, V_{ISO}		2.1			V
$V_{HYS\ (UVLO)}$	UVLO threshold hysteresis on V_{CC}, V_{ISO}			0.2		V
V_{ITH}	Input pin rising threshold				0.7	V_{SI}
V_{ITL}	Input pin falling threshold		0.3			V_{SI}
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)		0.1			V_{SI}
I_{IL}	Low level input current	V_{IL} = 0 at INx or SEL	–10			µA
I_{IH}	High level input current	V_{IH} = V_{SI}(1) at INx or SEL			10	µA
V_{OH}	High level output voltage	I_O = –4 mA, see 图 32	V_{SO}(1) – 0.4	V_{SO} – 0.2		V
V_{OL}	Low level output voltage	I_O = 4 mA, see 图 32		0.2	0.4	V
CMTI	Common mode transient immunity	V_I = V_{SI} or 0 V, V_{CM} = 1000 V; see 图 33	100			kV/us
I_{CC_SC}	DC current from supply under short circuit on V_{ISO}	V_{ISO} shorted to GND2		137		mA
$V_{ISO(RIP)}$	Output ripple on isolated supply (pk-pk)	20-MHz bandwidth, C_{LOAD} = 0.1 µF || 20 µF, I_{ISO} = 130 mA		100		mV

(1) V_{SI} = input side supply; V_{SO} = output side supply

7.10 Supply Current Characteristics—5-V Input, 5-V Output

V_{CC} = 5 V ±10%, SEL shorted to V_{ISO} (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7840						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7840); $V_I = V_{SI}$ (1) (ISOW7840 with F suffix)		23		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7840); V_I = 0 V (ISOW7840 with F suffix)		17		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		21		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		56		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7840); $V_I = V_{SI}$ (ISOW7840 with F suffix)	128			mA
		$V_I = V_{SI}$ (ISOW7840); V_I = 0 V (ISOW7840 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	128			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	111			
ISOW7841						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7841); $V_I = V_{SI}$ (1) (ISOW7841 with F suffix)		23		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7841); V_I = 0 V (ISOW7841 with F suffix)		17		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		20		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		54		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7841); $V_I = V_{SI}$ (ISOW7841 with F suffix)	128			mA
		$V_I = V_{SI}$ (ISOW7841); V_I = 0 V (ISOW7841 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	128			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	112			

(1) V_{SI} = input side supply; V_{SO} = output side supply
(2) Current available to load should be derated by 2 mA/°C for T_A > 80°C.

Supply Current Characteristics—5-V Input, 5-V Output (continued)

V_{CC} = 5 V ±10%, SEL shorted to V_{ISO} (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7842						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7842); V_I = V_{SI} (1) (ISOW7842 with F suffix)		24		mA
		No external I_{LOAD}; V_I = V_{SI} (ISOW7842); V_I = 0 V (ISOW7842 with F suffix)		18		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		21		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		51		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7842); V_I = V_{SI} (ISOW7842 with F suffix)	126			mA
		V_I = V_{SI} (ISOW7842); V_I = 0 V (ISOW7842 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	128			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	116			
ISOW7843						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7843); V_I = V_{SI} (1) (ISOW7843 with F suffix)		25		mA
		No external I_{LOAD}; V_I = V_{SI} (ISOW7843); V_I = 0 V (ISOW7843 with F suffix)		17		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		21		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		48		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7843); V_I = V_{SI} (ISOW7843 with F suffix)	125			mA
		V_I = V_{SI} (ISOW7843); V_I = 0 V (ISOW7843 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	126			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	120			

Supply Current Characteristics—5-V Input, 5-V Output (continued)

V_{CC} = 5 V ±10%, SEL shorted to V_{ISO} (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7844						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7844); $V_I = V_{SI}$ (1) (ISOW7844 with F suffix)		26		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7844); V_I = 0 V (ISOW7844 with F suffix)		17		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		22		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		46		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7844); $V_I = V_{SI}$ (ISOW7844 with F suffix)	123			mA
		$V_I = V_{SI}$ (ISOW7844); V_I = 0 V (ISOW7844 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	126			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	126			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	126			

7.11 Electrical Characteristics—5-V Input, 3.3-V Output

V_{CC} = 5 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{ISO}	Isolated supply voltage	External I_{ISO} = 0 to 50 mA	3.13	3.34	3.56	V
		External I_{ISO} = 0 to 130 mA	3	3.34	3.56	
$V_{ISO(LINE)}$	DC line regulation	I_{ISO} = 50 mA, V_{CC} = 4.5 V to 5.5 V		2		mV/V
$V_{ISO(LOAD)}$	DC load regulation	I_{ISO} = 10 to 130 mA		1%		
EFF	Efficiency at maximum load current	I_{ISO} = 130 mA, C_{LOAD} = 0.1 µF || 10 µF; V_I = V_{SI} (ISOW784x); V_I = 0 V (ISOW784x with F suffix)		48%		
$V_{CC+(UVLO)}$	Positive-going UVLO threshold on V_{CC}, V_{ISO}				2.7	V
$V_{CC–(UVLO)}$	Negative-going UVLO threshold on V_{CC}, V_{ISO}		2.1			V
$V_{HYS\ (UVLO)}$	UVLO threshold hysteresis on V_{CC}, V_{ISO}			0.2		V
V_{ITH}	Input pin rising threshold				0.7	V_{SI}
V_{ITL}	Input pin falling threshold		0.3			V_{SI}
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)		0.1			V_{SI}
I_{IL}	Low level input current	V_{IL} = 0 at INx or SEL	–10			µA
I_{IH}	High level input current	V_{IH} = V_{SI} (1) at INx or SEL			10	µA
V_{OH}	High level output voltage	I_O = –2 mA, see 图 32	V_{SO} (1) – 0.3	V_{SO} – 0.1		V
V_{OL}	Low level output voltage	I_O = 2 mA, see 图 32		0.1	0.3	V
CMTI	Common mode transient immunity	V_I = V_{SI} or 0 V, V_{CM} = 1000 V; see 图 33	100			kV/us
I_{CC_SC}	DC current from supply under short circuit on V_{ISO}	V_{ISO} shorted to GND2		137		mA
$V_{ISO(RIP)}$	Output ripple on isolated supply (pk-pk)	20-MHz bandwidth, C_{LOAD} = 0.1 µF || 20 µF, I_{ISO} = 130 mA		100		mV

(1) V_{SI} = input side supply; V_{SO} = output side supply

7.12 Supply Current Characteristics—5-V Input, 3.3-V Output

V_{CC} = 5 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7840						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7840); $V_I = V_{SI}$ (1) (ISOW7840 with F suffix)		20		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7840); V_I = 0 V (ISOW7840 with F suffix)		15		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		17		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		19		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		39		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7840); $V_I = V_{SI}$ (ISOW7840 with F suffix)	128			mA
		$V_I = V_{SI}$ (ISOW7840); V_I = 0 V (ISOW7840 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	129			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	128			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	116			
ISOW7841						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7841); $V_I = V_{SI}$ (1) (ISOW7841 with F suffix)		20		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7841); V_I = 0 V (ISOW7841 with F suffix)		14		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		17		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		20		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		40		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7841); $V_I = V_{SI}$ (ISOW7841 with F suffix)	128			mA
		$V_I = V_{SI}$ (ISOW7841); V_I = 0 V (ISOW7841 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L= 15 pF	129			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	128			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	118			

(1) V_{SI} = input side supply; V_{SO} = output side supply
(2) Current available to load should be derated by 2 mA/°C for T_A > 105°C.

Supply Current Characteristics—5-V Input, 3.3-V Output (continued)

V_{CC} = 5 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7842						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7842); $V_I = V_{SI}$ (1) (ISOW7842 with F suffix)		20		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7842); V_I = 0 V (ISOW7842 with F suffix)		15		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		18		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		20		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		39		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7842); $V_I = V_{SI}$ (ISOW7842 with F suffix)	126			mA
		$V_I = V_{SI}$ (ISOW7842); V_I = 0V (ISOW7842 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	128			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	119			
ISOW7843						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7843); $V_I = V_{SI}$ (1) (ISOW7843 with F suffix)		20		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7843); V_I = 0 V (ISOW7843 with F suffix)		14		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		18		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		20		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		39		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7843); $V_I = V_{SI}$ (ISOW7843 with F suffix)	125			mA
		$V_I = V_{SI}$ (ISOW7843); V_I = 0 V (ISOW7843 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	127			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	123			

Supply Current Characteristics—5-V Input, 3.3-V Output (continued)

V_{CC} = 5 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7844						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7844); $V_I = V_{SI}$ (1) (ISOW7844 with F suffix)		21		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7844); V_I = 0 V (ISOW7844 with F suffix)		15		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		18		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		20		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		41		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7844); $V_I = V_{SI}$ (ISOW7844 with F suffix)	123			mA
		$V_I = V_{SI}$ (ISOW7844); V_I = 0 V (ISOW7844 with F suffix)	130			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	126			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	126			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	126			

7.13 Electrical Characteristics—3.3-V Input, 3.3-V Output

V_{CC} = 3.3 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{ISO}	Isolated supply voltage	External I_{ISO} = 0 to 30 mA	3.13	3.34	3.58	V
		External I_{ISO} = 0 to 75 mA	3	3.34	3.58	
$V_{ISO(LINE)}$	DC line regulation	I_{ISO} = 30 mA, V_{CC} = 3 V to 3.6 V		2		mV/V
$V_{ISO(LOAD)}$	DC load regulation	I_{ISO} = 0 to 75 mA		1%		
EFF	Efficiency at maximum load current	I_{ISO} = 75 mA, C_{LOAD} = 0.1 µF || 10 µF; V_I = V_{SI} (ISOW784x); V_I = 0 V (ISOW784x with F suffix)		47%		
$V_{CC+(UVLO)}$	Positive-going UVLO threshold on V_{CC}, V_{ISO}				2.7	V
$V_{CC–(UVLO)}$	Negative-going UVLO threshold on V_{CC}, V_{ISO}		2.1			V
$V_{HYS\ (UVLO)}$	UVLO threshold hysteresis on V_{CC}, V_{ISO}			0.2		V
V_{ITH}	Input pin rising threshold				0.7	V_{SI}
V_{ITL}	Input pin falling threshold		0.3			V_{SI}
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)		0.1			V_{SI}
I_{IL}	Low level input current	V_{IL} = 0 at INx or SEL	–10			µA
I_{IH}	High level input current	V_{IH} = V_{SI} (1) at INx or SEL			10	µA
V_{OH}	High level output voltage	I_O = –2 mA, see 图 32	V_{SO} (1) – 0.3	V_{SO} – 0.1		V
V_{OL}	Low level output voltage	I_O = 2 mA, see 图 32		0.1	0.3	V
CMTI	Common mode transient immunity	V_I = V_{SI} or 0 V, V_{CM} = 1000 V; see 图 33	100			kV/us
I_{CC_SC}	DC current from supply under short circuit on V_{ISO}	V_{ISO} shorted to GND2		143		mA
$V_{ISO(RIP)}$	Output ripple on isolated supply (pk-pk)	20-MHz bandwidth, C_{LOAD} = 0.1 µF || 20 µF, I_{ISO} = 75 mA		90		mV

(1) V_{SI}= input side supply; V_{SO} = output side supply

7.14 Supply Current Characteristics—3.3-V Input, 3.3-V Output

V_{CC} = 3.3 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7840						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7840); $V_I = V_{SI}$ (1) (ISOW7840 with F suffix)		26		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7840); V_I = 0 V (ISOW7840 with F suffix)		20		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		23		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		26		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		54		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7840); $V_I = V_{SI}$ (ISOW7840 with F suffix)	73			mA
		$V_I = V_{SI}$ (ISOW7840); V_I = 0 V (ISOW7840 with F suffix)	75			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	74			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	73			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	61			
ISOW7841						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7841); $V_I = V_{SI}$ (1) (ISOW7841 with F suffix)		26		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7841); V_I = 0 V (ISOW7841 with F suffix)		20		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		23		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		26		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		53		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7841); $V_I = V_{SI}$ (ISOW7841 with F suffix)	73			mA
		$V_I = V_{SI}$(ISOW7841); V_I = 0 V (ISOW7841 with F suffix)	75			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	74			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	73			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	61			

(1) V_{SI} = input side supply; V_{SO} = output side supply
(2) Current available to load should be derated by 2 mA/°C for T_A > 115°C.

Supply Current Characteristics—3.3-V Input, 3.3-V Output (continued)

V_{CC} = 3.3 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7842						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7842); $V_I = V_{SI}$ (1) (ISOW7842 with F suffix)		28		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7842); V_I = 0 V (ISOW7842 with F suffix)		20		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		26		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		49		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7842); $V_I = V_{SI}$ (ISOW7842 with F suffix)	71			mA
		$V_I = V_{SI}$ (ISOW7842); V_I= 0 V (ISOW7842 with F suffix)	75			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	73			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	72			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	64			
ISOW7843						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7843); $V_I = V_{SI}$ (1) (ISOW7843 with F suffix)		28		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7843); V_I = 0 V (ISOW7843 with F suffix)		19		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		24		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		26		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		45		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7843); $V_I = V_{SI}$ (ISOW7843 with F suffix)	70			mA
		$V_I = V_{SI}$ (ISOW7843); V_I = 0 V (ISOW7843 with F suffix)	75			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	72			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	72			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	68			

Supply Current Characteristics—3.3-V Input, 3.3-V Output (continued)

V_{CC} = 3.3 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISOW7844						
I_{CC}	Current drawn from supply	No external I_{LOAD}; V_I = 0 V (ISOW7844); $V_I = V_{SI}$ (1) (ISOW7844 with F suffix)		30		mA
		No external I_{LOAD}; $V_I = V_{SI}$ (ISOW7844); V_I = 0 V (ISOW7844 with F suffix)		19		
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF, No external I_{LOAD}		25		
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF, No external I_{LOAD}		26		
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF, No external I_{LOAD}		42		
$I_{ISO(OUT)}$ (2)	Current available to isolated supply	V_I = 0 V (ISOW7844); $V_I = V_{SI}$ (ISOW7844 with F suffix)	68			mA
		$V_I = V_{SI}$ (ISOW7844); V_I = 0 V (ISOW7844 with F suffix)	75			
		All channels switching with square wave clock input of 1 Mbps; C_L = 15 pF	71			
		All channels switching with square wave clock input of 10 Mbps; C_L = 15 pF	71			
		All channels switching with square wave clock input of 100 Mbps; C_L = 15 pF	71			

7.15 Switching Characteristics—5-V Input, 5-V Output

V_{CC} = 5 V ±10%, SEL shorted to V_{ISO} (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See 图 32		13	17.6	ns
PWD	Pulse width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$			0.6	4.7	ns
$t_{SK(o)}$	Channel-channel output skew time(2)	Same-direction channels			2.5	ns
$t_{SK(p-p)}$	Part-part skew time(3)				4.5	ns
t_r, t_f	Output signal rise and fall times			2	4	ns

(1) Also known as pulse skew.
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.16 Switching Characteristics—5-V Input, 3.3-V Output

V_{CC} = 5 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See 图 32		14	19.7	ns
PWD	Pulse width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$			0.6	4.4	ns
$t_{SK(o)}$	Channel-channel output skew time(2)	Same-direction channels			2	ns
$t_{SK(p-p)}$	Part-part skew time(3)				4.5	ns
t_r, t_f	Output signal rise and fall times			1	4	ns

(1) Also known as pulse skew.
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.17 Switching Characteristics—3.3-V Input, 3.3-V Output

V_{CC} = 3.3 V ±10%, SEL shorted to GND2 (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See 图 32		14.5	20.2	ns
PWD	Pulse width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$			0.6	4.4	ns
$t_{SK(o)}$	Channel-channel output skew time(2)	Same-direction channels			2.2	ns
$t_{SK(p-p)}$	Part-part skew time(3)				4.5	ns
t_r, t_f	Output signal rise and fall times			1	3	ns

(1) Also known as pulse skew.
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.18 Insulation Characteristics Curves

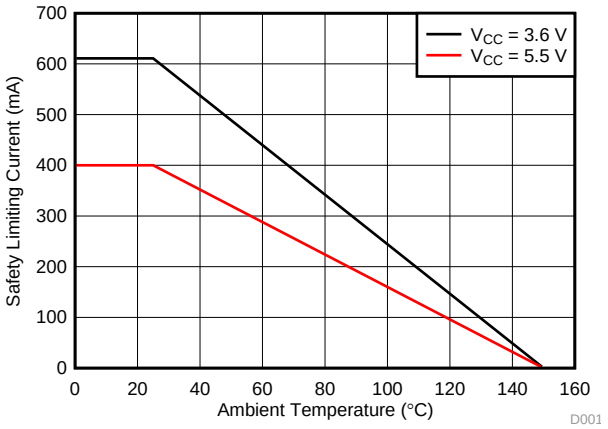


图 1. Thermal Derating Curve for Safety Limiting Current per VDE

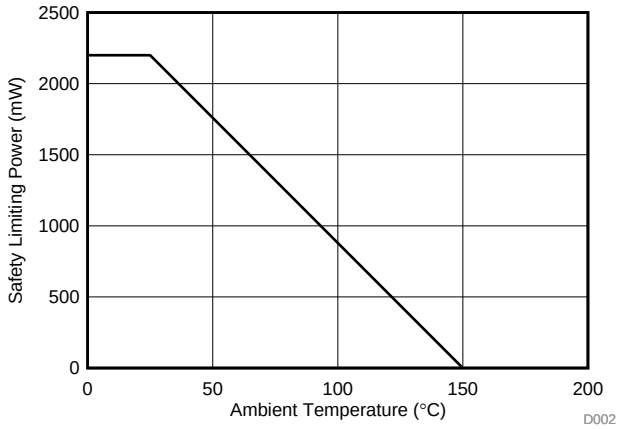
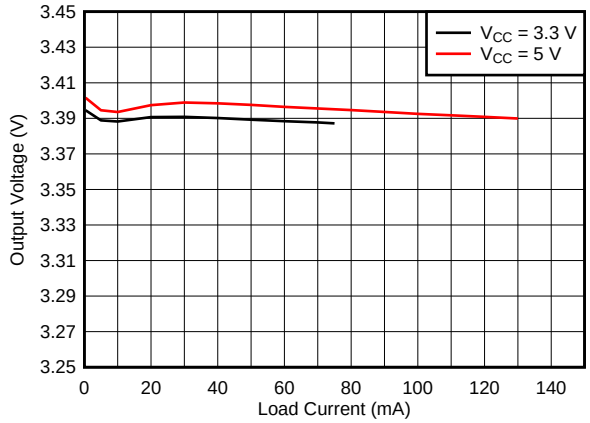


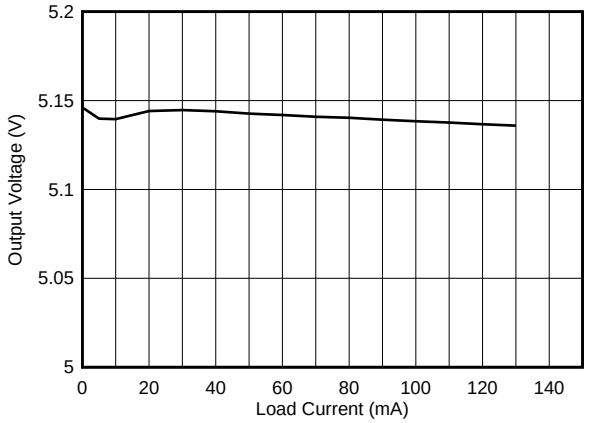
图 2. Thermal Derating Curve for Safety Limiting Power per VDE

7.19 Typical Characteristics



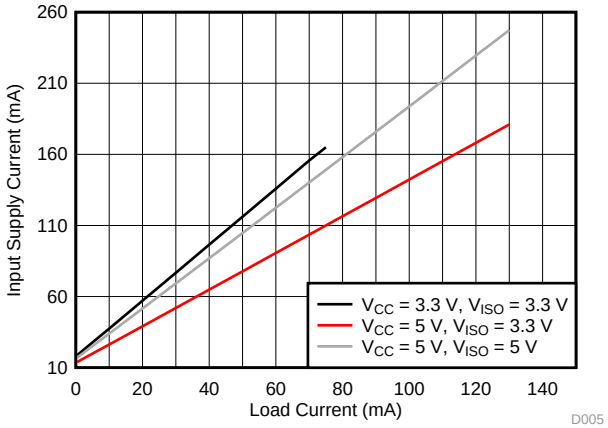
V_{ISO} = 3.3 V T_A = 25°C

图 3. Isolated Supply Voltage (V_{ISO}) vs Load Current (I_{ISO})



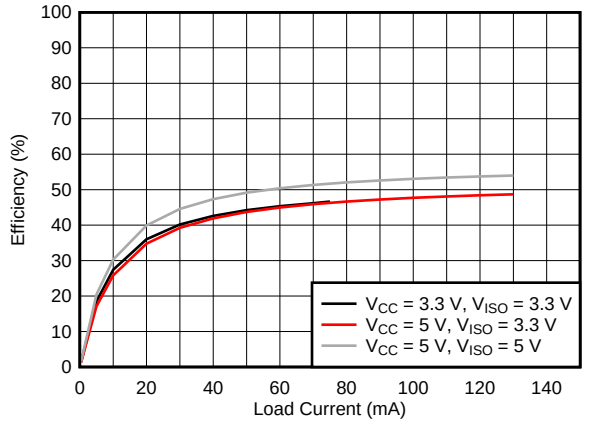
V_{ISO} = 5 V T_A = 25°C

图 4. Isolated Supply Voltage (V_{ISO}) vs Load Current (I_{ISO})



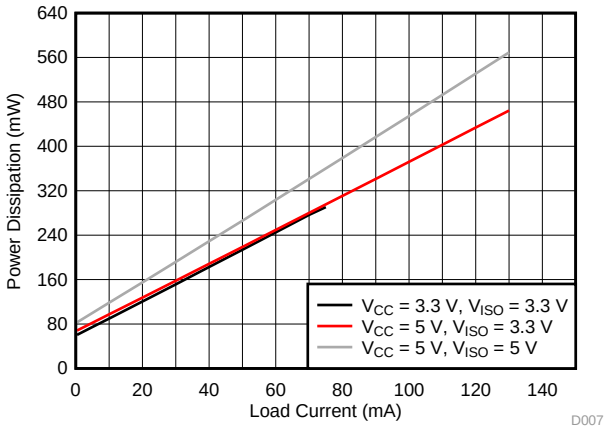
T_A = 25°C

图 5. ISOW7841 Supply Current (I_{CC}) vs Load Current (I_{ISO})



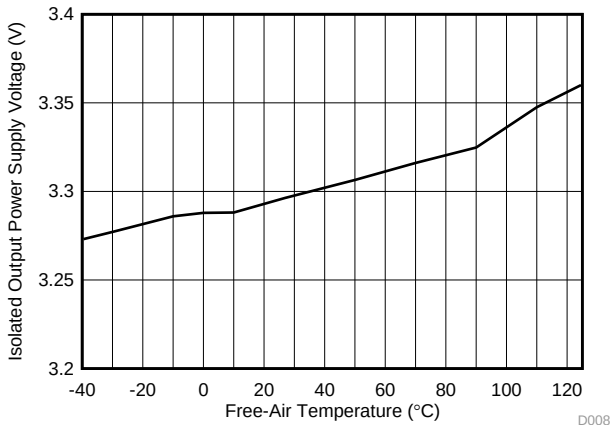
T_A = 25°C

图 6. ISOW7841 Efficiency vs Load Current (I_{ISO})



T_A = 25°C

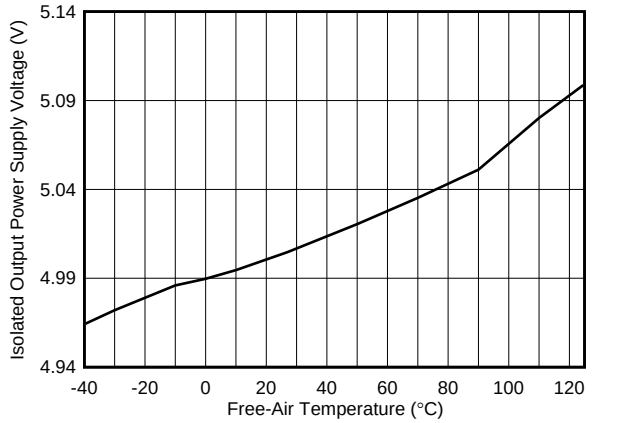
图 7. ISOW7841 Power Dissipation vs Load Current (I_{ISO})



No I_{ISO} load V_{CC} = 5 V V_{ISO} = 3.3 V

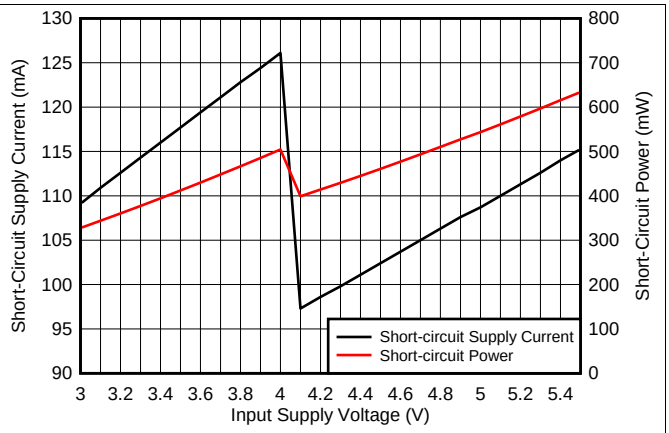
图 8. 3.3-V Isolated Supply Voltage (V_{ISO}) vs Free-Air Temperature

Typical Characteristics (接下页)



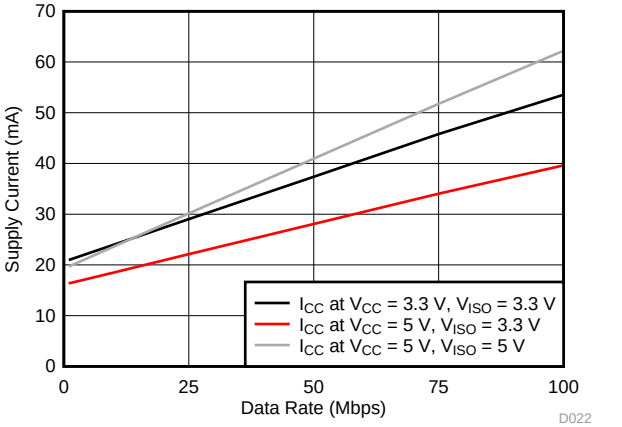
No I_{ISO} load V_{CC} = 5 V V_{ISO} = 5 V

图 9. 5-V Isolated Supply Voltage (V_{ISO}) vs Free-Air Temperature



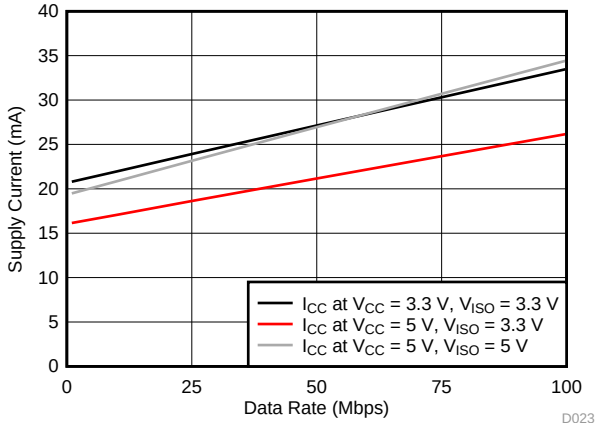
V_{ISO} shorted to GND2 T_A = 25°C

图 10. Short-Circuit Supply Current (I_{CC}) and Power (P) vs Supply Voltage (V_{CC})



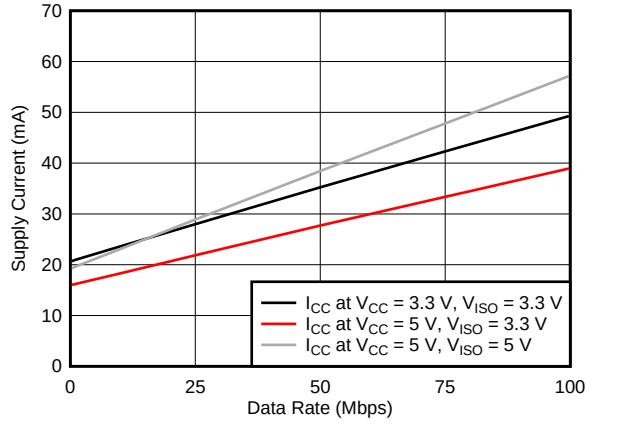
C_L = 15 pF T_A = 25°C No I_{ISO} load

图 11. ISOW7840 Supply Current vs Data Rate



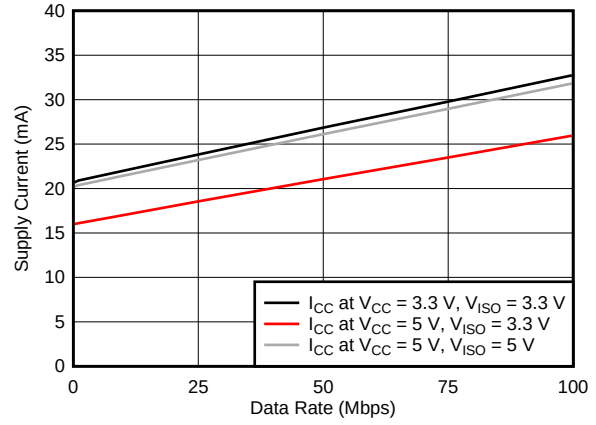
C_L = no load T_A = 25°C No I_{ISO} load

图 12. ISOW7840 Supply Current vs Data Rate



C_L = 15 pF T_A = 25°C No I_{ISO} load

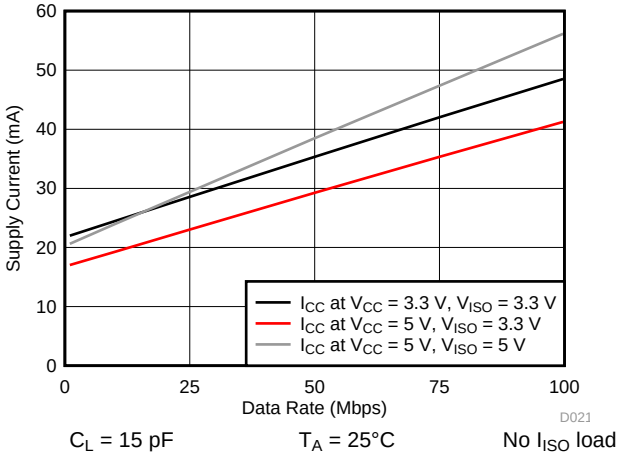
图 13. ISOW7841 Supply Current vs Data Rate



C_L = no load T_A = 25°C No I_{ISO} load

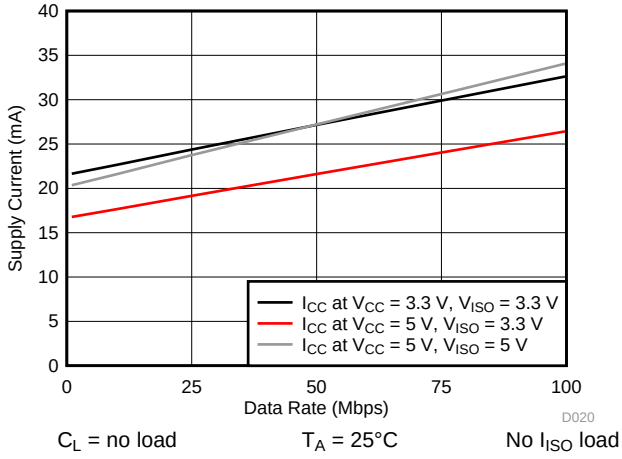
图 14. ISOW7841 Supply Current vs Data Rate

Typical Characteristics (接下页)



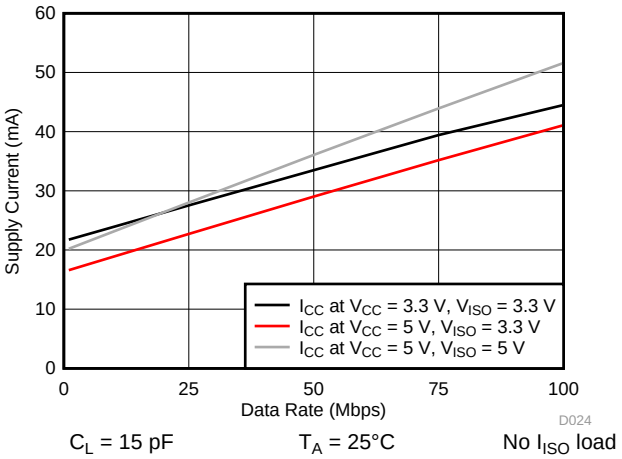
C_L = 15 pF T_A = 25°C No I_{ISO} load

图 15. ISOW7842 Supply Current vs Data Rate



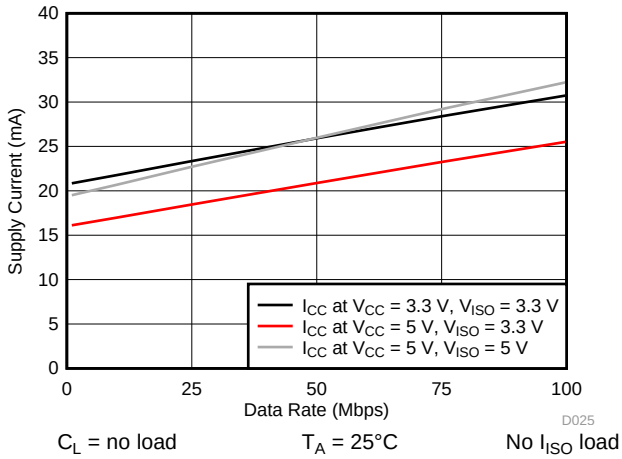
C_L = no load T_A = 25°C No I_{ISO} load

图 16. ISOW7842 Supply Current vs Data Rate



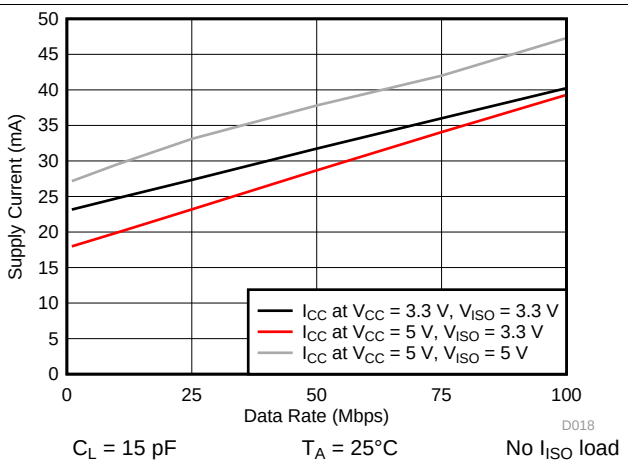
C_L = 15 pF T_A = 25°C No I_{ISO} load

图 17. ISOW7843 Supply Current vs Data Rate



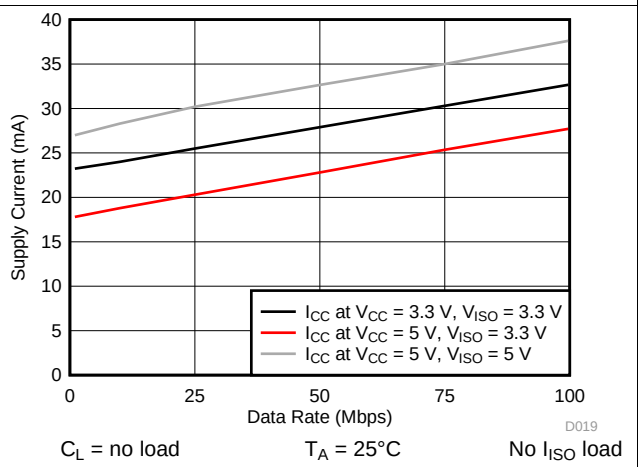
C_L = no load T_A = 25°C No I_{ISO} load

图 18. ISOW7843 Supply Current vs Data Rate



C_L = 15 pF T_A = 25°C No I_{ISO} load

图 19. ISOW7844 Supply Current vs Data Rate



C_L = no load T_A = 25°C No I_{ISO} load

图 20. ISOW7844 Supply Current vs Data Rate

Typical Characteristics (接下页)

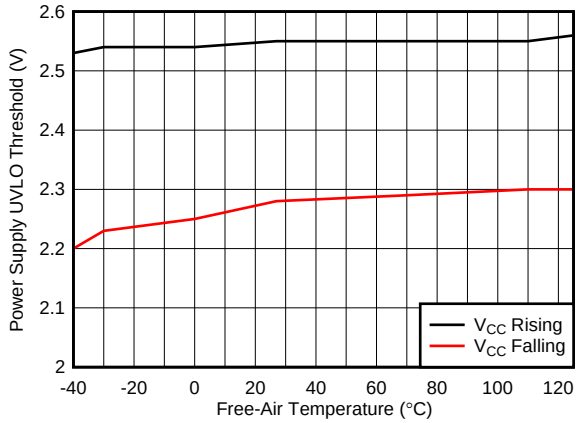


图 21. Power-Supply Undervoltage Threshold vs Free Air Temperature

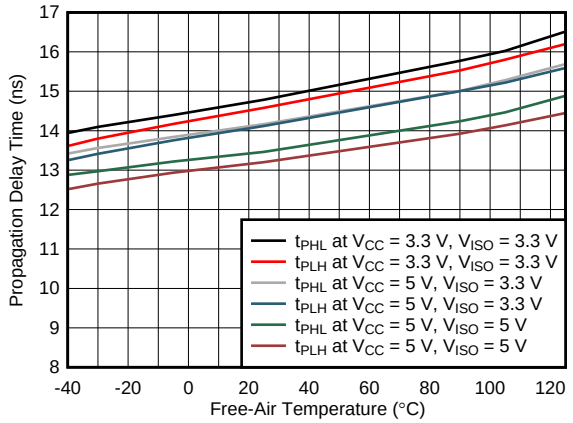
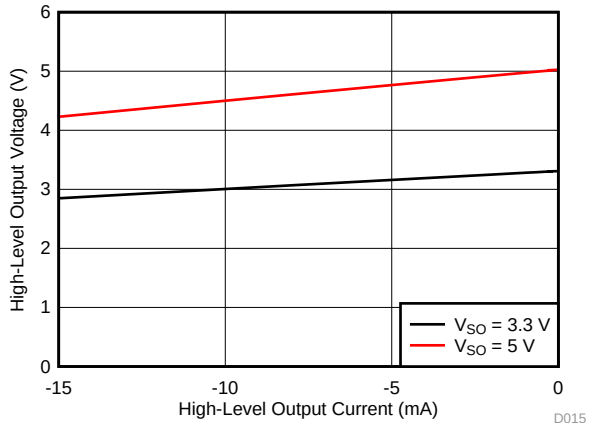
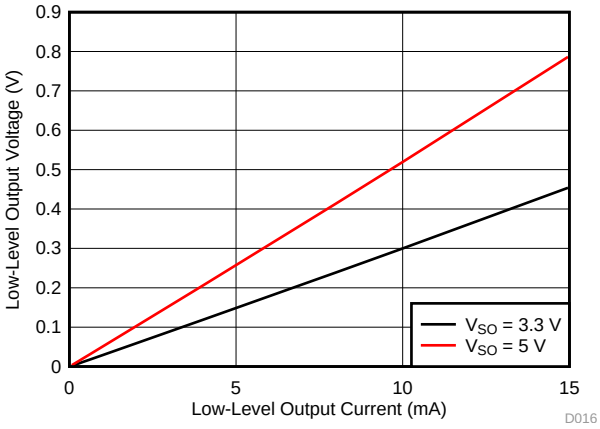


图 22. Propagation Delay Time vs Free-Air Temperature



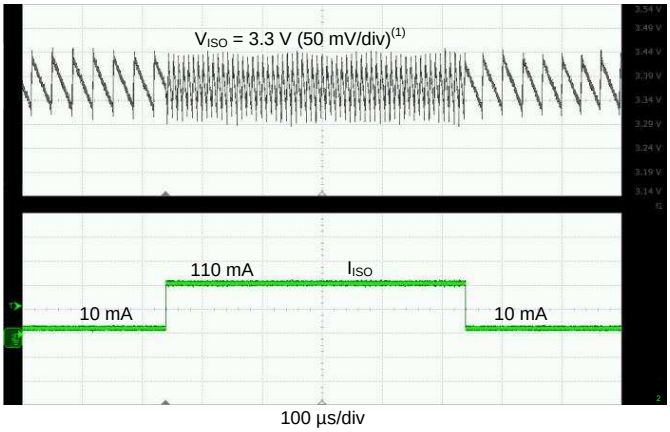
TA = 25°C

图 23. High-Level Output Voltage vs High-Level Output Current



TA = 25°C

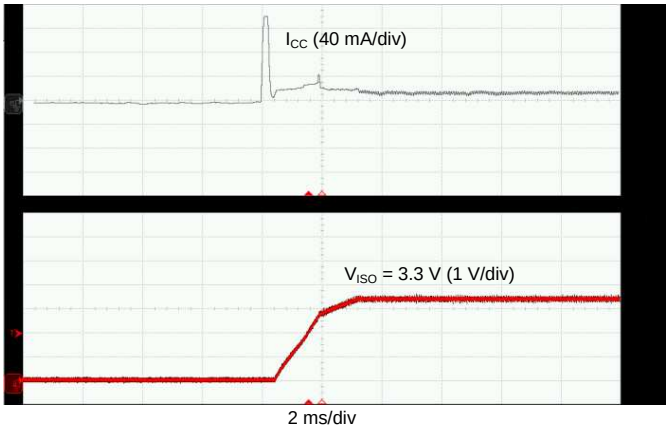
图 24. Low-Level Output Voltage vs Low-Level Output Current



VCC = 5 V VISO = 3.3 V

Negligible undershoot and overshoot because of load transient

图 25. 10-mA to 110-mA Load Transient Response

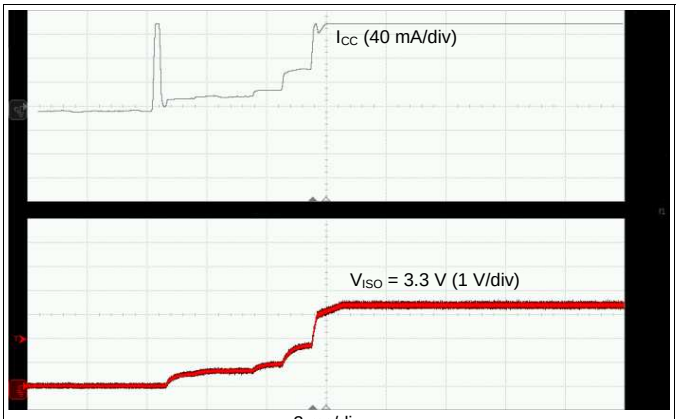


VCC = 5 V VISO = 3.3 V

Current spike is because of charging the input supply capacitor

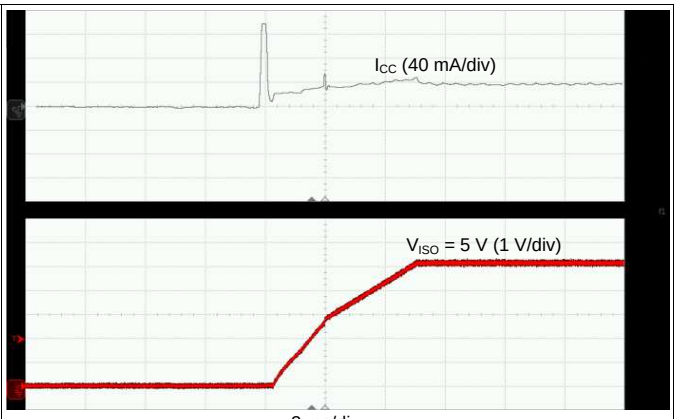
图 26. Soft Start at 10-mA Load

Typical Characteristics (接下页)



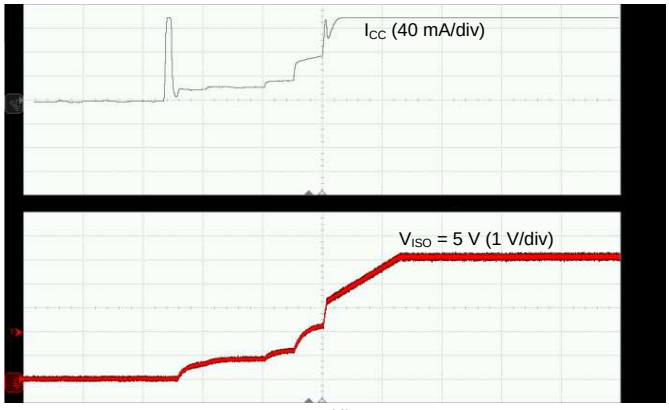
V_{CC} = 5 V V_{ISO} = 3.3 V
Input current spike is because of charging the input supply decoupling capacitor

图 27. Soft Start at 120-mA Load



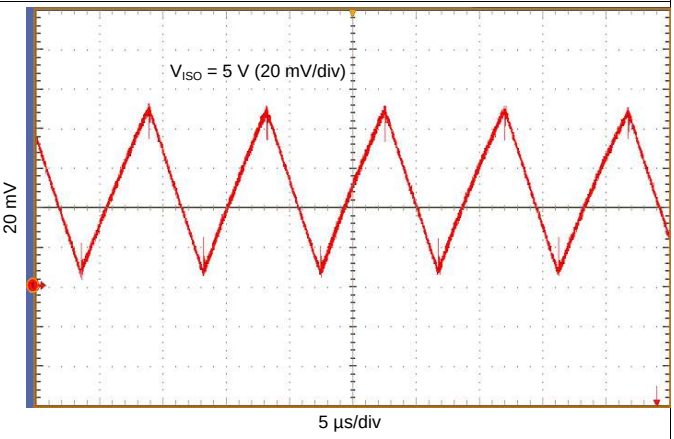
V_{CC} = 5 V V_{ISO} = 5 V
Input current spike is because of charging the input supply decoupling capacitor

图 28. Soft Start at 10-mA Load



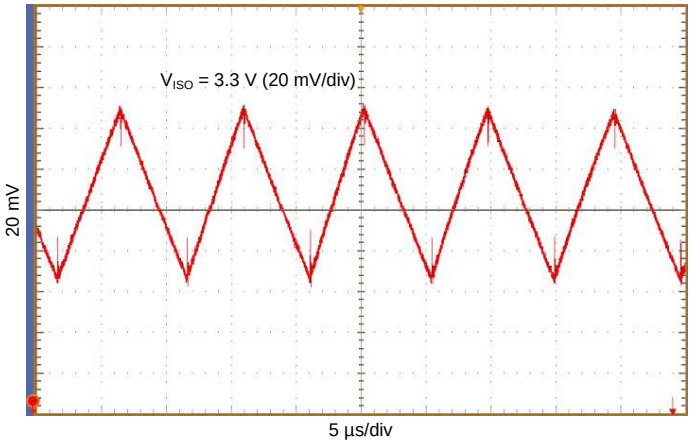
V_{CC} = 5 V V_{ISO} = 5 V
Input current spike is because of charging the input supply decoupling capacitor

图 29. Soft Start at 130-mA Load



V_{CC} = 5 V V_{ISO} = 5 V

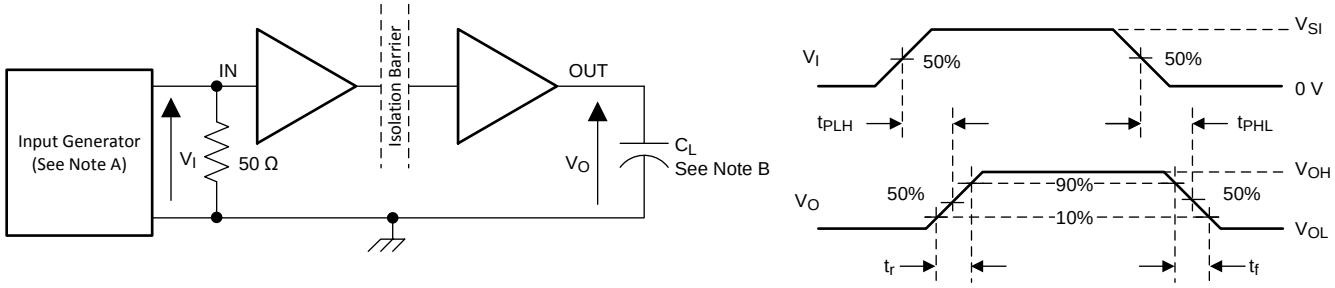
图 30. V_{ISO} Ripple Voltage at 130 mA



V_{CC} = 5 V V_{ISO} = 3.3 V

图 31. V_{ISO} Ripple Voltage at 130 mA

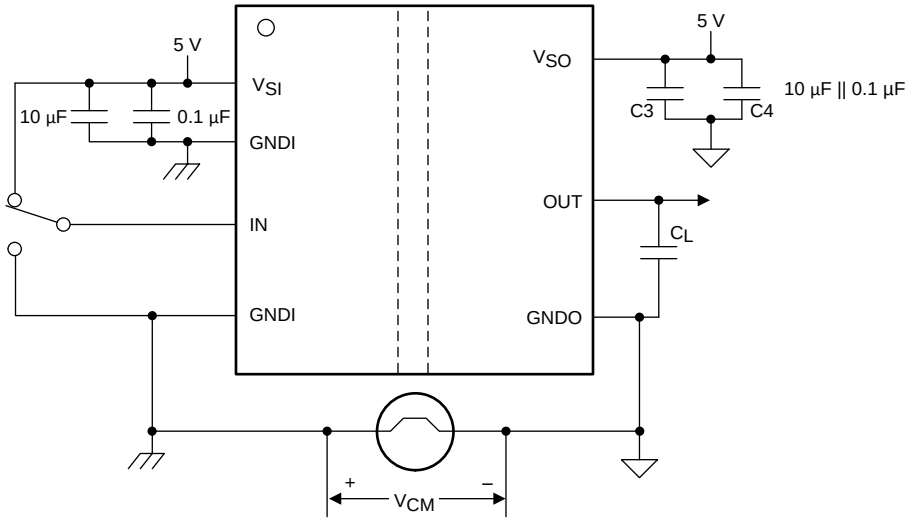
8 Parameter Measurement Information



The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50 Ω. At the input, 50-Ω resistor is required to terminate the input generator signal. The resistor is not required in the actual application.

C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

图 32. Switching Characteristics Test Circuit and Voltage Waveforms



C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations.

Pass-fail criteria: Outputs must remain stable.

图 33. Common-Mode Transient Immunity Test Circuit

9 Detailed Description

9.1 Overview

The ISOW784x family of devices has a high-efficiency, low-emissions isolated DC-DC converter, and four high-speed isolated data channels. 图 34 shows the functional block diagram of the ISOW784x family of devices.

The integrated DC-DC converter uses switched mode operation and proprietary circuit techniques to reduce power losses and boost efficiency. Specialized control mechanisms, clocking schemes, and the use of a high-Q on-chip transformer provide high efficiency and low radiated emissions. The integrated transformer uses thin film polymer as the insulation barrier.

The V_{CC} supply is provided to the primary power controller that switches the power stage connected to the integrated transformer. Power is transferred to the secondary side, rectified and regulated to either 3.3 V or 5 V, depending on the SEL pin. The output voltage, V_{ISO}, is monitored and feedback information is conveyed to the primary side through a dedicated isolation channel. The duty cycle of the primary switching stage is adjusted accordingly. The fast feedback control loop of the power converter ensures low overshoots and undershoots during load transients. Undervoltage lockout (UVLO) with hysteresis is integrated on the V_{CC} and V_{ISO} supplies which ensures robust system performance under noisy conditions. An integrated soft-start mechanism ensures controlled inrush current and avoids any overshoot on the output during power up.

The integrated signal-isolation channels employ an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon-dioxide based isolation barrier. The transmitter sends a high-frequency carrier across the barrier to represent one state and sends no signal to represent the other state. The receiver demodulates the signal after signal conditioning and produces the output through a buffer stage. The signal-isolation channels incorporate advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions from the high frequency carrier and IO buffer switching. 图 35 shows a functional block diagram of a typical signal isolation channel.

The ISOW784x family of devices is suitable for applications that have limited board space and require more integration. This family of devices is also suitable for very-high voltage applications, where power transformers meeting the required isolation specifications are bulky and expensive.

9.2 Functional Block Diagram

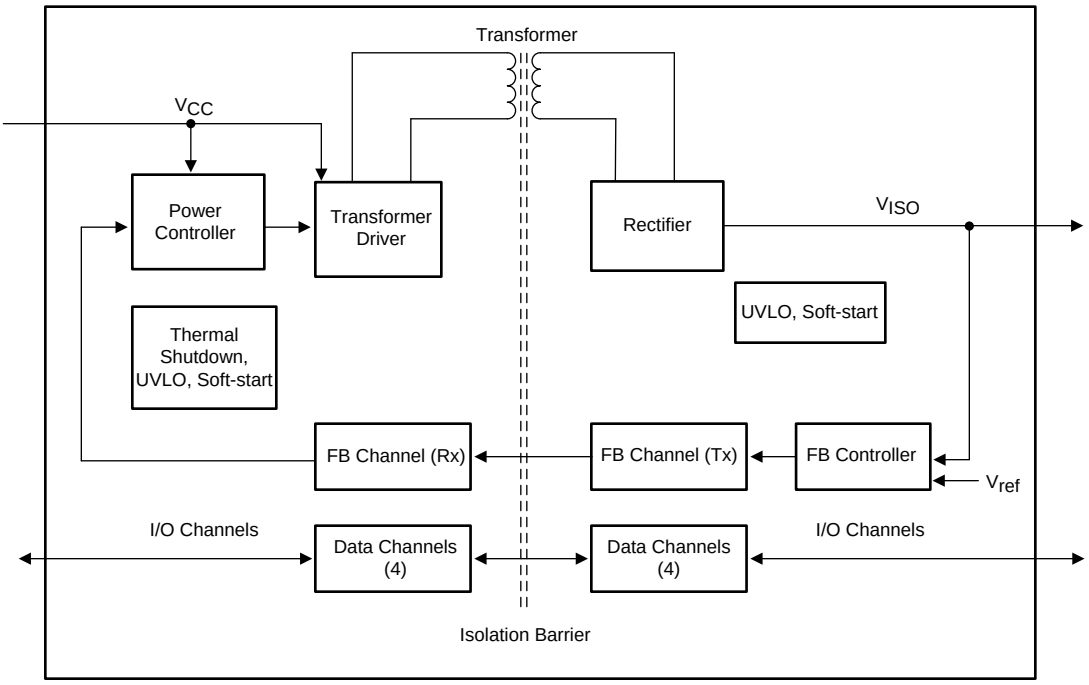


图 34. Block Diagram

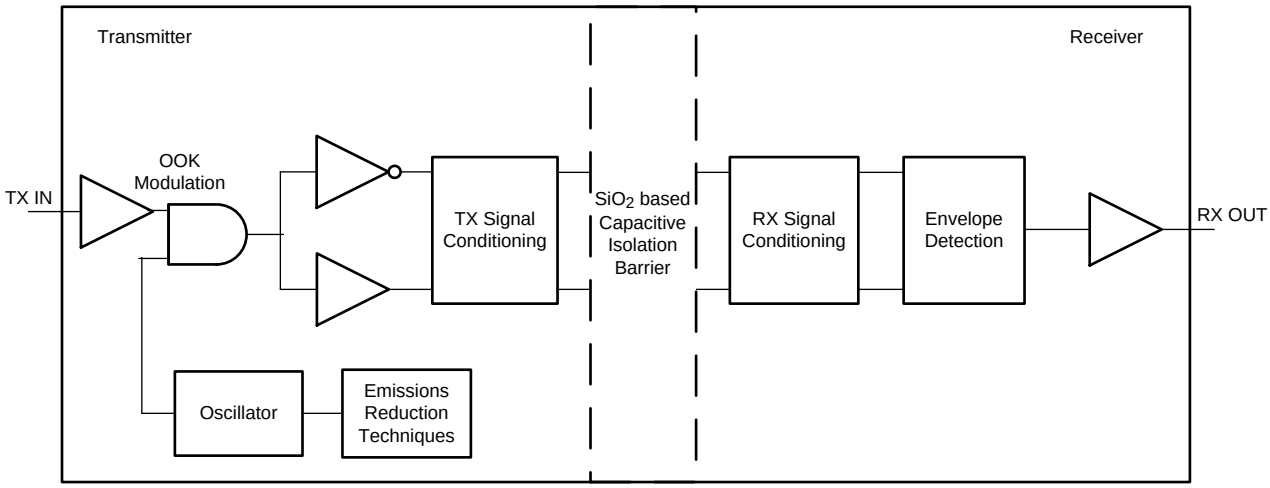


图 35. Conceptual Block Diagram of a Capacitive Data Channel

Functional Block Diagram (接下页)

图 36 shows a conceptual detail of how the OOK scheme works.

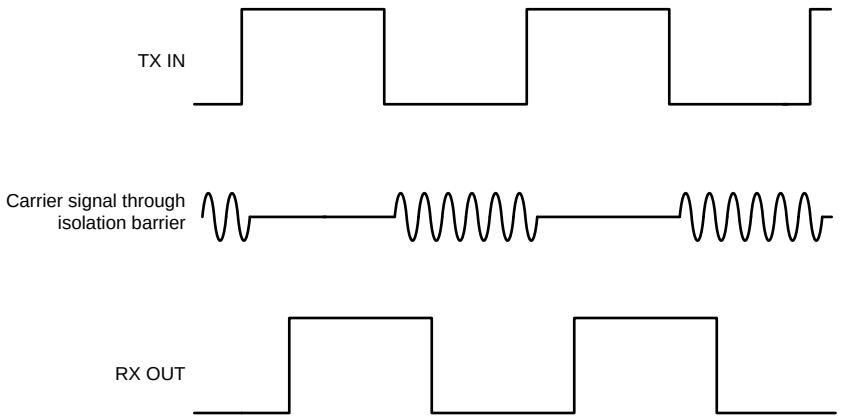


图 36. On-Off Keying (OOK) Based Modulation Scheme

9.3 Feature Description

表 1 shows an overview of the device features.

表 1. Device Features

PART NUMBER(1)	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT STATE	RATED ISOLATION(2)
ISOW7840	4 forward, 0 reverse	100 Mbps	High	5 kV_{RMS} / 7071 V_{PK}
ISOW7840F			Low	
ISOW7841	3 forward, 1 reverse		High	
ISOW7841F			Low	
ISOW7842	2 forward, 2 reverse		High	
ISOW7842F			Low	
ISOW7843	1 forward, 3 reverse		High	
ISOW7843F			Low	
ISOW7844	0 forward, 4 reverse		High	
ISOW7844F			Low	

(1) The F suffix is part of the orderable part number. See the *机械、封装和可订购信息* section for the full orderable part number.
(2) For detailed isolation ratings, see the *Safety-Related Certifications* table.

9.3.1 Electromagnetic Compatibility (EMC) Considerations

The ISOW784x family of devices uses emissions reduction schemes for the internal oscillator and advanced internal layout scheme to minimize radiated emissions at the system level.

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISOW784x family of devices incorporates many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.

- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.

9.3.2 Power-Up and Power-Down Behavior

The ISOW784x family of devices has built-in UVLO on the V_{CC} and V_{ISO} supplies with positive-going and negative-going thresholds and hysteresis. When the V_{CC} voltage crosses the positive-going UVLO threshold during power-up, the DC-DC converter initializes and the power converter duty cycle is increased in a controlled manner. This soft-start scheme limits primary peak currents drawn from the V_{CC} supply and charges the V_{ISO} output in a controlled manner, avoiding overshoots. Outputs of the isolated data channels are in an indeterminate state until the V_{CC} or V_{ISO} voltage crosses the positive-going UVLO threshold. When the UVLO positive-going threshold is crossed on the secondary side V_{ISO} pin, the feedback data channel starts providing feedback to the primary controller. The regulation loop takes over and the isolated data channels go to the normal state defined by the respective input channels or their default states. Design should consider a sufficient time margin (typically 10 ms with 10-µF load capacitance) to allow this power up sequence before valid data channels are accounted for system functionality.

When V_{CC} power is lost, the primary side DC-DC controller turns off when the UVLO lower threshold is reached. The V_{ISO} capacitor then discharges depending on the external load. The isolated data outputs on the V_{ISO} side are returned to the default state for the brief time that the V_{ISO} voltage takes to discharge to zero.

9.3.3 Current Limit, Thermal Overload Protection

The ISOW784x family of devices is protected against output overload and short circuit. Output voltage starts dropping when the power converter is not able to deliver the current demanded during overload conditions. For a V_{ISO} short-circuit to ground, the duty cycle of the converter is limited to help protect against any damage.

Thermal protection is also integrated to help prevent the device from getting damaged during overload and short-circuit conditions on the isolated output. Under these conditions, the device temperature starts to increase. When the temperature goes above 180°C, thermal shutdown activates and the primary controller turns off which removes the energy supplied to the V_{ISO} load, which causes the device to cool off. When the junction temperature goes below 150°C, the device starts to function normally. If an overload or output short-circuit condition prevails, this protection cycle is repeated. Care should be taken in the design to prevent the device junction temperatures from reaching such high values.

9.4 Device Functional Modes

表 2 lists the supply configurations for these devices.

表 2. Supply Configurations

SEL INPUT	V_{CC}	V_{ISO}
Shorted to V_{ISO}	5 V	5 V
Shorted to GND2 or floating	5 V	3.3 V
Shorted to GND2 or floating	3.3 V(1)	3.3 V(2)

(1) V_{CC} = 3.3 V, SEL shorted to V_{ISO} (essentially V_{ISO} = 5 V) is not recommended mode of configuration.
(2) The SEL pin has a weak pulldown internally. Therefore for V_{ISO} = 3.3 V, the SEL pin should be strongly connected to the GND2 pin in noisy system scenarios.

表 3 lists the functional modes for ISOW784x devices.

表 3. Function Table(1)

INPUT SUPPLY (V_{CC})	INPUT (INx)	OUTPUT (OUTx)	COMMENTS
PU	H	H	Output channel assumes the logic state of its input
	L	L	
	Open	Default	Default mode(2): When INx is open, the corresponding output channel assumes logic based on default output mode of selected version
PD	X	Undetermined(3)	

(1) PU = Powered up (V_{CC} ≥ 2.7 V); PD = Powered down (V_{CC} < 2.1 V); X = Irrelevant; H = High level; L = Low level, V_{CC} = Input-side supply
(2) In the default condition, the output is high for ISOW784x and low for ISOW784x with the F suffix.
(3) The outputs are in an undetermined state when V_{CC} < 2.1 V.

9.4.1 Device I/O Schematics

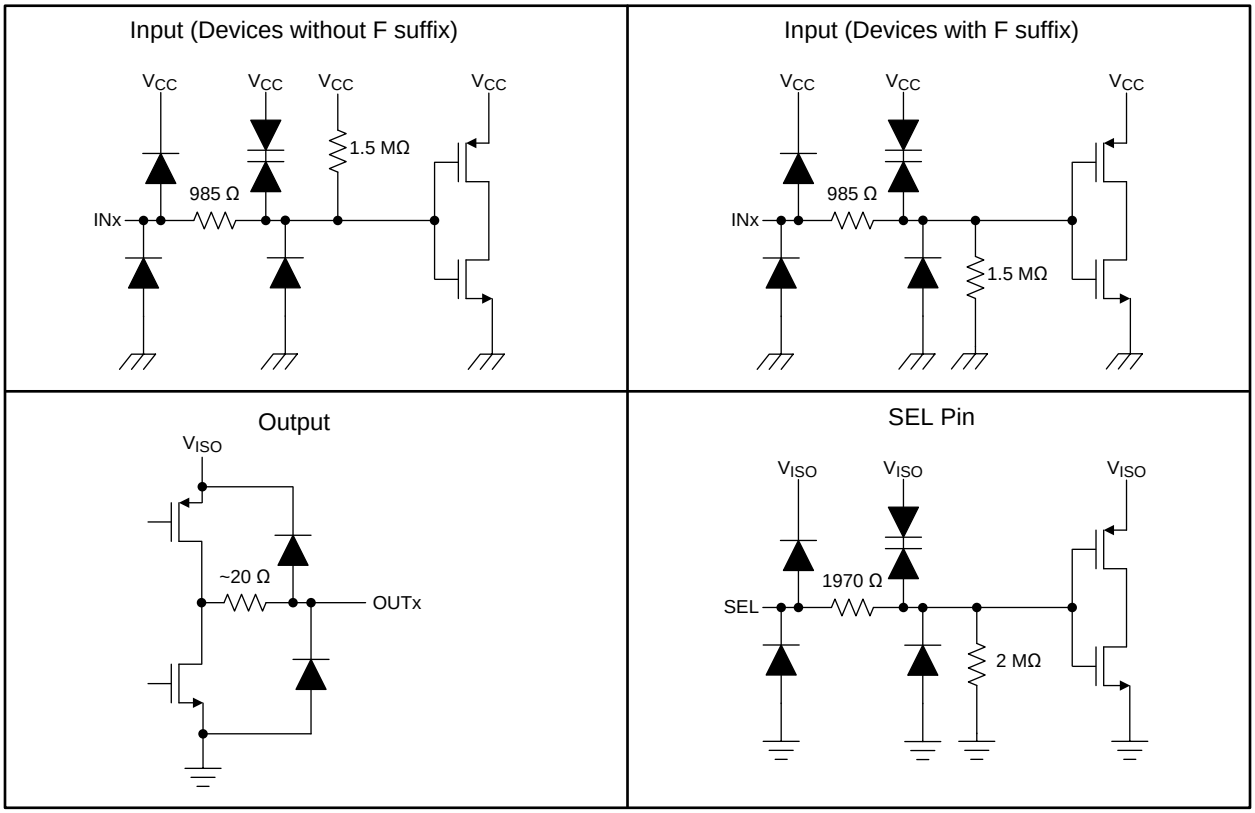


图 37. Device I/O Schematics

10 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

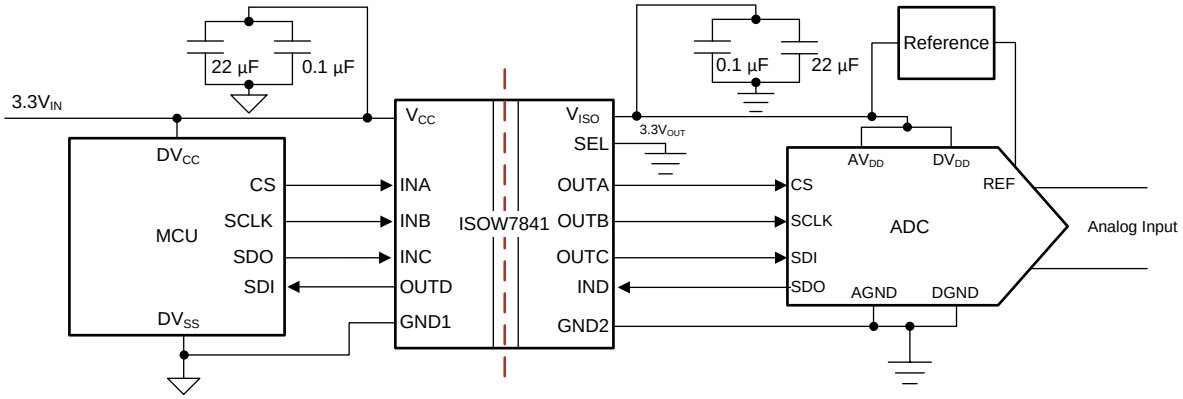
The device is a high-performance, quad channel digital isolator with integrated DC-DC converter. Typically digital isolators require two power supplies isolated from each other to power up both sides of device. Due to the integrated DC-DC converter in the device, the isolated supply is generated inside the device that can be used to power isolated side of the device and peripherals on isolated side, thus saving board space. The device uses single-ended CMOS-logic switching technology. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is Microcontroller or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

The device is suitable for applications that have limited board space and desire more integration. The device isalso suitable for very high voltage applications, where power transformers meeting the required isolation specifications are bulky and expensive.

10.2 Typical Application

For step-by-step design procedure, circuit schematics, bill of materials, printed circuit board (PCB) files, simulation results, and test results, refer to TI Design TIDA-01333, *Eight-Channel, Isolated, High-Voltage Analog Input Module With ISOW7841 Reference Design*.

图 38 shows the typical schematic for SPI isolation.



Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations.

图 38. Isolated Power and SPI for ADC Sensing Application with ISOW7841

10.2.1 Design Requirements

To design with this device, use the parameters listed in 表 4.

表 4. Design Parameters

PARAMETER	VALUE
Input voltage	3 V to 5.5 V
Decoupling capacitor between V_{CC} and GND1	0.1 µF to 10 µF

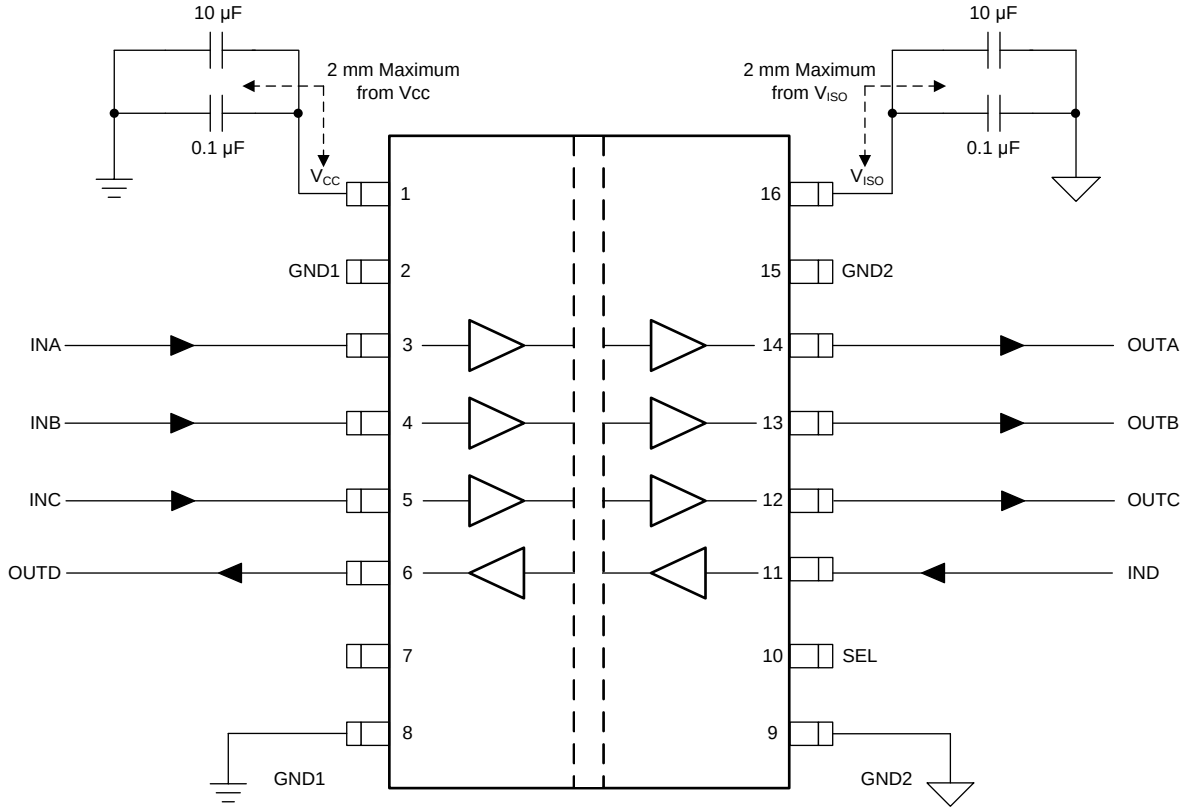
表 4. Design Parameters (接下页)

PARAMETER	VALUE
Decoupling capacitor between V_{ISO} and GND2	0.1 µF to 10 µF

Because of very-high current flowing through the ISOW7841 device V_{CC} and V_{ISO} supplies, higher decoupling capacitors typically provide better noise and ripple performance. Although a 10-µF capacitor is adequate, higher decoupling capacitors (such as 47 µF) on both the V_{CC} and V_{ISO} pins to the respective grounds are strongly recommended to achieve the best performance. Optional 100 µF decoupling capacitor can be added between V_{CC} and GND1 pins; refer to Power Supply Recommendations for more details.

10.2.2 Detailed Design Procedure

The devices requires only external bypass capacitors to operate. These low-ESR ceramic bypass capacitors must be placed as close to the chip pads as possible.



Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations.

图 39. Typical ISOW7841 Circuit Hook-Up

The V_{CC} power-supply input provides power to isolated data channels and to the isolated DC-DC converter. Use 公式 1 to calculate the total power budget on the primary side.

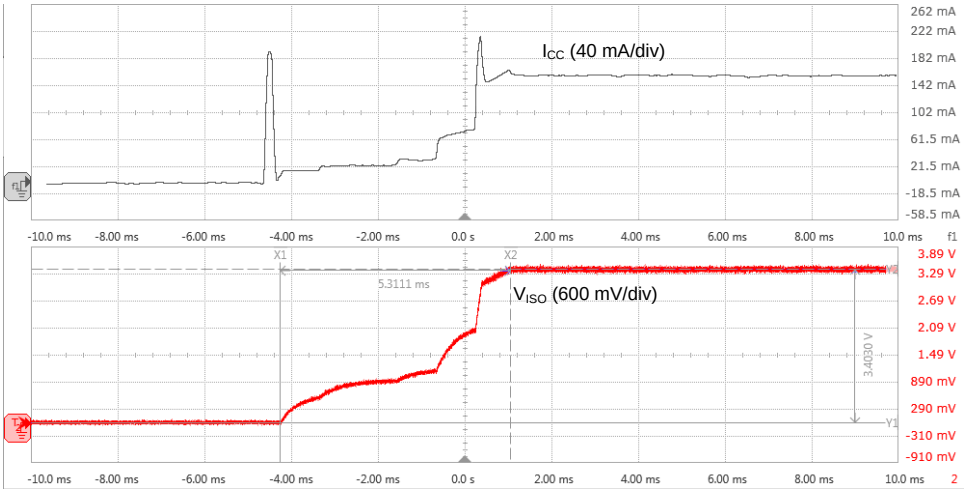
$$I_{CC} = (V_{ISO} \times I_{ISO}) / (\eta \times V_{CC}) + I_{inpx}$$

where

- I_{CC} is the total current required by the primary supply.
- V_{ISO} is the isolated supply voltage.
- I_{ISO} is the external load on the isolated supply voltage.
- η is the efficiency.
- V_{CC} is the supply voltage.
- I_{inpx} is the total current drawn for the isolated data channels and power converter when data channels are

toggling at a specific data rate. This data is shown in the *Electrical Characteristics—5-V Input, 5-V Output* table. (1)

10.2.3 Application Curve



V_{CC} = 3.3 V I_{ISO} = 70 mA

Input current spike is because of charging the input supply decoupling capacitor

图 40. Soft-Start Waveform

10.2.3.1 Insulation Lifetime

Insulation lifetime projection data is collected by using industry-standard Time Dependent Dielectric Breakdown (TDDB) test method. In this test, all pins on each side of the barrier are tied together creating a two-terminal device and high voltage applied between the two sides; See 图 41 for TDDB test setup. The insulation breakdown data is collected at various high voltages switching at 60 Hz over temperature. For reinforced insulation, VDE standard requires the use of TDDB projection line with failure rate of less than 1 part per million (ppm). Even though the expected minimum insulation lifetime is 20 years at the specified working isolation voltage, VDE reinforced certification requires additional safety margin of 20% for working voltage and 87.5% for lifetime which translates into minimum required insulation lifetime of 37.5 years at a working voltage that's 20% higher than the specified value.

图 42 shows the intrinsic capability of the isolation barrier to withstand high voltage stress over its lifetime. Based on the TDDB data, the intrinsic capability of the insulation is 1000 V_{RMS} with a lifetime of 1184 years.

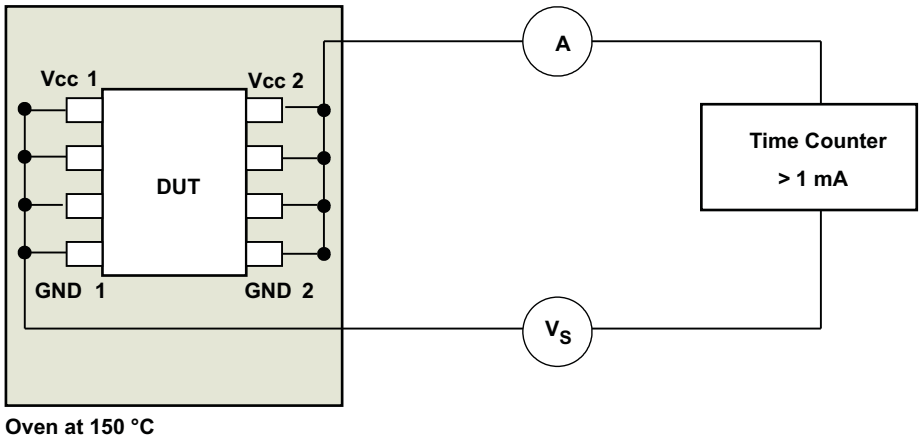


图 41. Test Setup for Insulation Lifetime Measurement

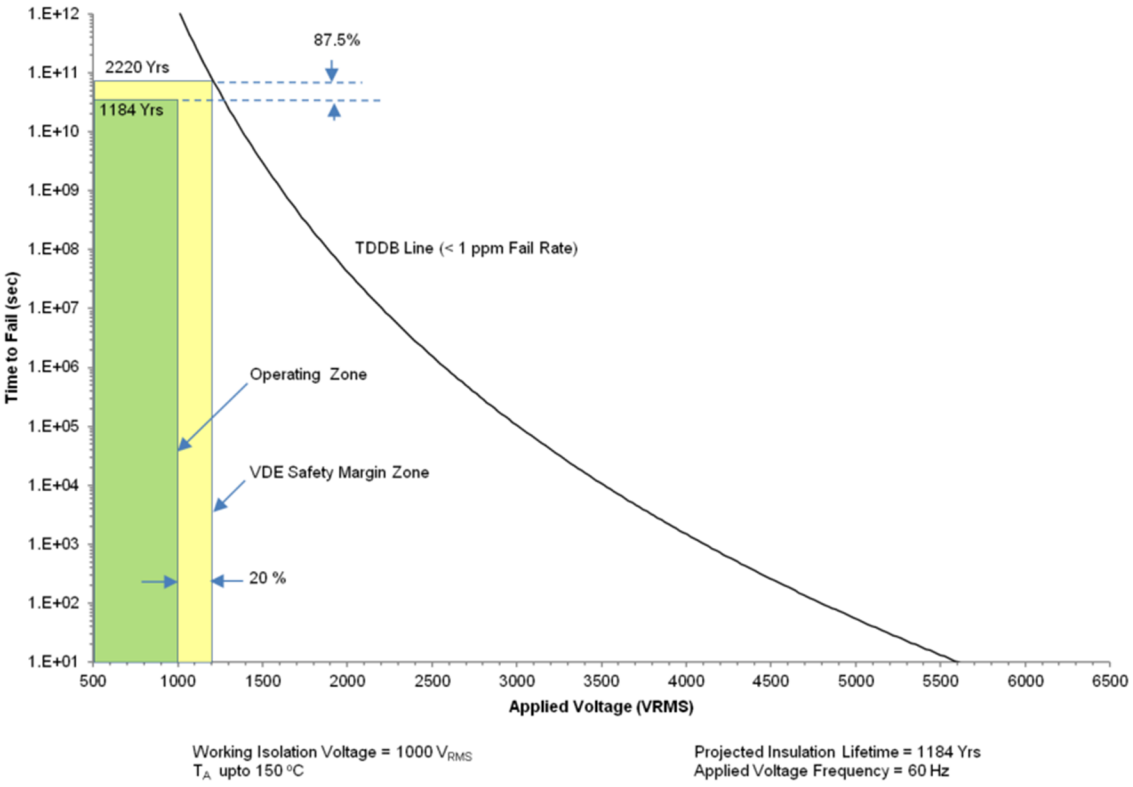


图 42. Insulation Lifetime Projection Data

11 Power Supply Recommendations

To help make sure that operation is reliable at data rates and supply voltages, adequate decoupling capacitors must be located as close to supply pins as possible. The input supply (V_{CC}) must have an appropriate current rating to support output load and switching at the maximum data rate required by the end application. For more information, refer to the *Detailed Design Procedure* section.

ISOW784x integrates a synchronous, isolated DC/DC converter along with isolated data channels. Due to finite efficiency of the integrated micro-transformer, for any given output load current, the input current will be proportionally higher. Thus, the input supply (V_{CC}) decoupling capacitor also needs to be sufficiently larger than the output supply (V_{ISO}) decoupling capacitor. It is recommended to have an input capacitor that is larger than the output capacitor by at least 100 µF. It is also recommended to have an input power supply to ISOW784x with sufficient current limit to support output load current requirements. For an output load current of 130 mA, it is recommended to have >600 mA of input current limit and for lower output load currents, the input current limit can be proportionally lower. When the input supply is lower than 2.7 V, the device can go into a protected under-voltage lock out (UVLO) state per the UVLO thresholds specified in datasheet. Under UVLO state, it is recommended that the output voltage also be discharged to less than 2.1 V. This can be accomplished by having an input capacitor that is 100 µF larger compared to the output capacitor. It also helps to have a small load (~10 mA) at the output capacitor to bleed off any unwanted, residual charge. To make sure ISOW784x quickly transitions from UVLO state to powered state, it is recommended to have an input supply rise time of less than 10 ms.

If it is not possible to follow the aforementioned recommendations and frequent brownouts are expected on the input supply, then simple secondary side monitoring, protection and reset components can help improve the robustness of overall system and power-up or reset mechanisms. More details on output monitoring, protection and an example of reset mechanism can be found in *Overvoltage protection for isolated DC/DC converter*

12 Layout

12.1 Layout Guidelines

A minimum of four layers is required to accomplish a low-EMI PCB design (see 图 43). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane, and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in^2.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.
- Keep decoupling capacitors as close as possible to the V_{CC} and V_{ISO} pins.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

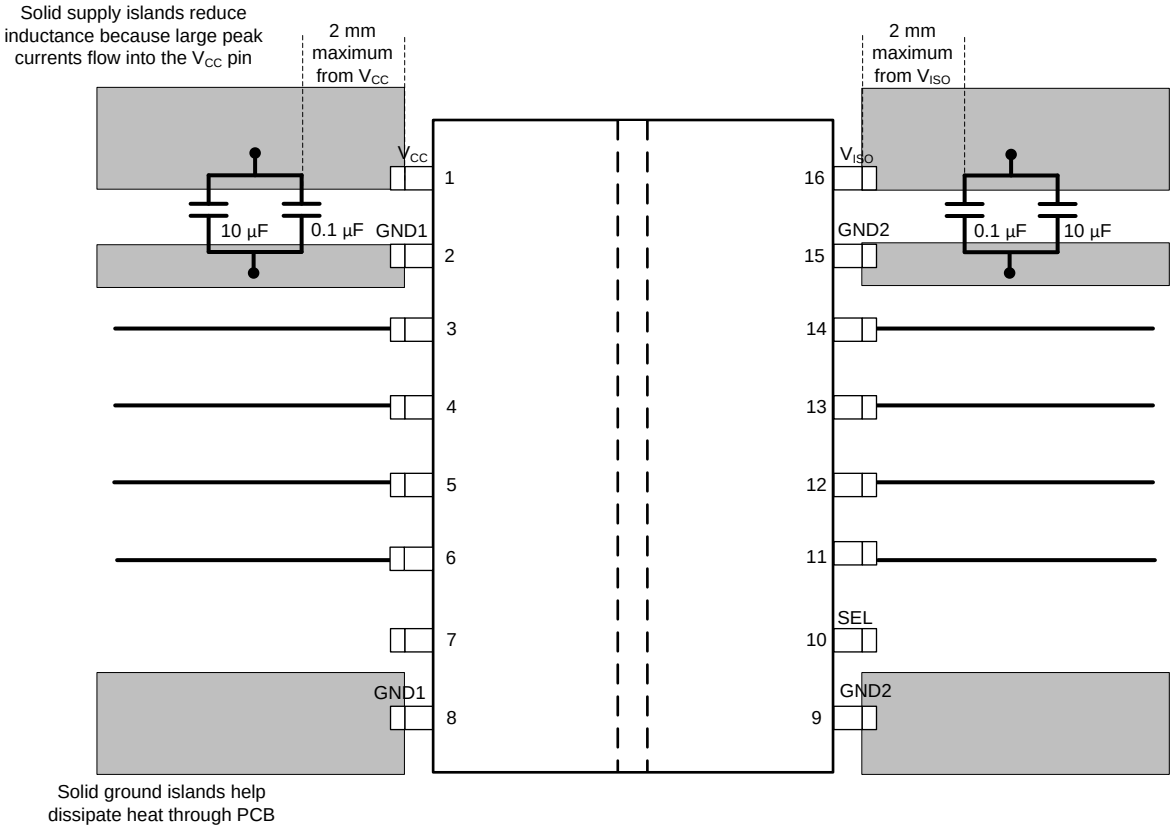
Because the device has no thermal pad to dissipate heat, the device dissipates heat through the respective GND pins. Ensure that enough copper is present on both GND pins to prevent the internal junction temperature of the device from rising to unacceptable levels.

The integrated signal and power isolation device simplifies system design and reduces board area. The use of low-inductance micro-transformers in the device necessitates the use of high frequency switching, resulting in higher radiated emissions compared to discrete solutions. The device uses on-chip circuit techniques to reduce emissions compared to competing solutions. For further reduction in radiated emissions at system level, refer to the *Low-Emission Designs With ISOW7841 Integrated Signal and Power Isolator* application report.

12.1.1 PCB Material

For digital circuit boards operating at less than 150 Mbps, (or rise and fall times greater than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

12.2 Layout Example



Optional 100 µF capacitor can be added between V_{CC} and GND1; refer to Power Supply Recommendations.

图 43. Layout Example

13 器件和文档支持

13.1 器件支持

13.1.1 开发支持

有关开发支持，请参阅：

- 《采用 ISOW7841 的 8 通道隔离式高电压模拟输入模块参考设计》
- 《具有集成信号和电源的隔离式 RS-485 参考设计》
- 《具有集成信号和电源的隔离式 RS-232 参考设计》

13.2 文档支持

13.2.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI)，*《数字隔离器设计指南》*
- 德州仪器 (TI)，*《隔离相关术语》*
- 德州仪器 (TI)，*《具有集成直流/直流转换器的 ISOW784x 四通道数字隔离器评估模块》*用户指南
- 德州仪器 (TI)，*《采用 ISOW7841 集成信号和电源隔离器的低排放设计》*应用报告

13.3 相关链接

下表列出了快速访问链接。类别包括技术文档、支持与社区资源、工具和软件，以及申请样片或购买产品的快速链接。

表 **5.** 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
ISOW7840	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISOW7841	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISOW7842	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISOW7843	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
ISOW7844	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

13.4 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的*通知我* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

13.5 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.6 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

13.7 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

13.8 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

14 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISOW7840DWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7840	Samples
ISOW7840DWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7840	Samples
ISOW7840FDWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7840F	Samples
ISOW7840FDWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7840F	Samples
ISOW7841DWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7841	Samples
ISOW7841DWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7841	Samples
ISOW7841FDWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7841F	Samples
ISOW7841FDWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7841F	Samples
ISOW7842DWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7842	Samples
ISOW7842DWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7842	Samples
ISOW7842FDWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7842F	Samples
ISOW7842FDWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7842F	Samples
ISOW7843DWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7843	Samples
ISOW7843DWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7843	Samples
ISOW7843FDWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7843F	Samples
ISOW7843FDWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7843F	Samples
ISOW7844DWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7844	Samples
ISOW7844DWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7844	Samples
ISOW7844FDWE	ACTIVE	SOIC	DWE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7844F	Samples
ISOW7844FDWER	ACTIVE	SOIC	DWE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7844F	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

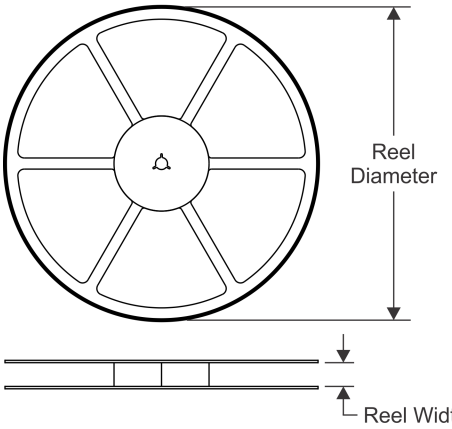
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

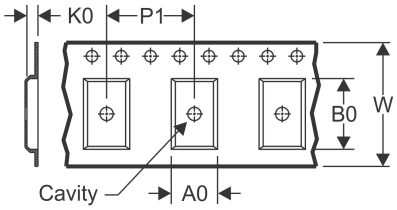
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

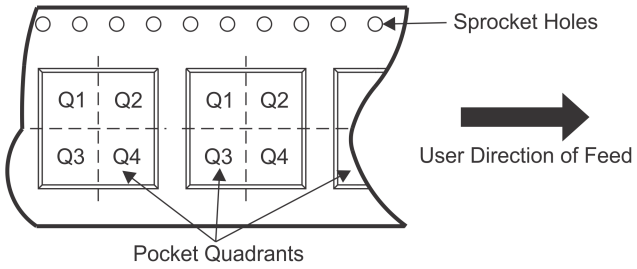


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

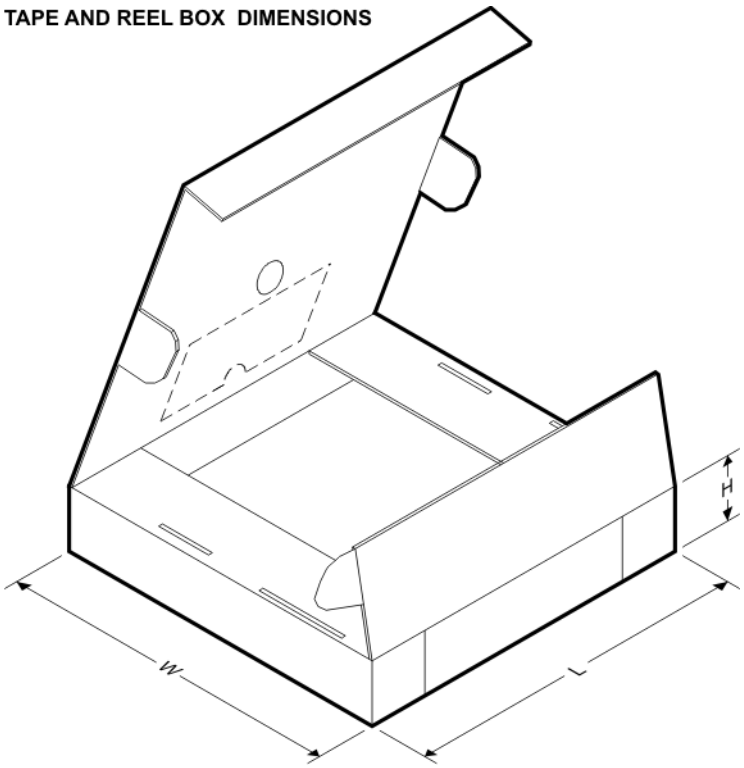
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISOW7840DWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7840FDWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7841DWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7841FDWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7842DWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7842FDWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7843DWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7843FDWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7844DWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISOW7844FDWER	SOIC	DWE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

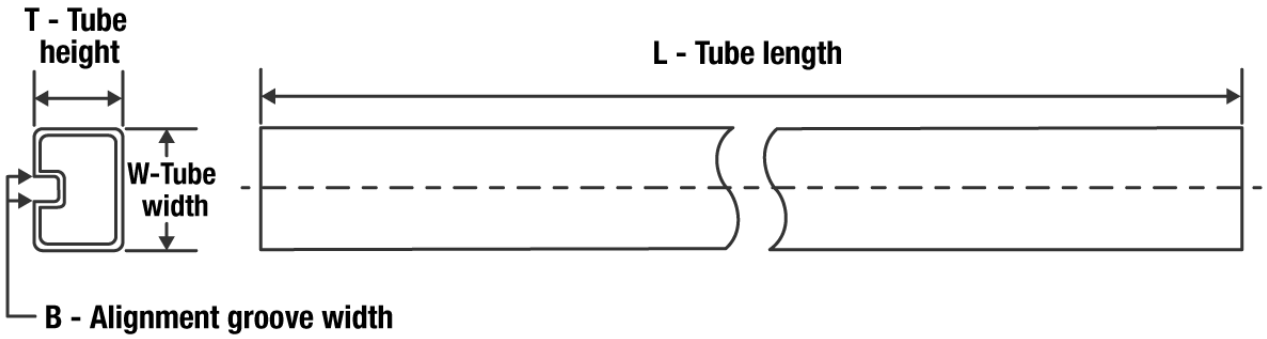
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

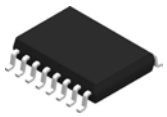
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISOW7840DWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7840FDWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7841DWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7841FDWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7842DWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7842FDWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7843DWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7843FDWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7844DWER	SOIC	DWE	16	2000	350.0	350.0	43.0
ISOW7844FDWER	SOIC	DWE	16	2000	350.0	350.0	43.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
ISOW7840DWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7840FDWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7841DWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7841FDWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7842DWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7842FDWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7843DWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7843FDWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7844DWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6
ISOW7844FDWE	DWE	SO-MOD	16	40	506.98	12.7	4826	6.6

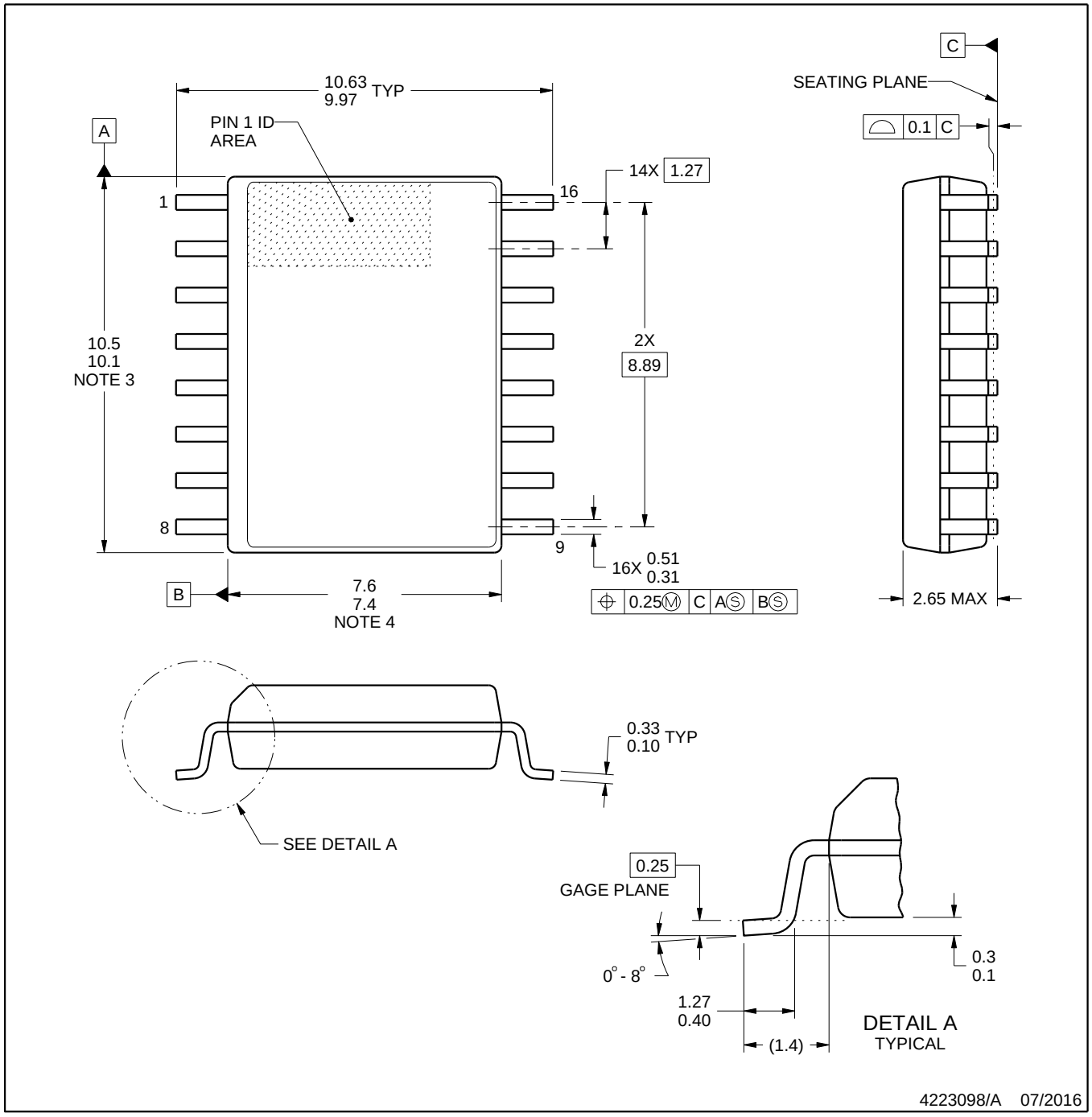


PACKAGE OUTLINE

DWE0016A

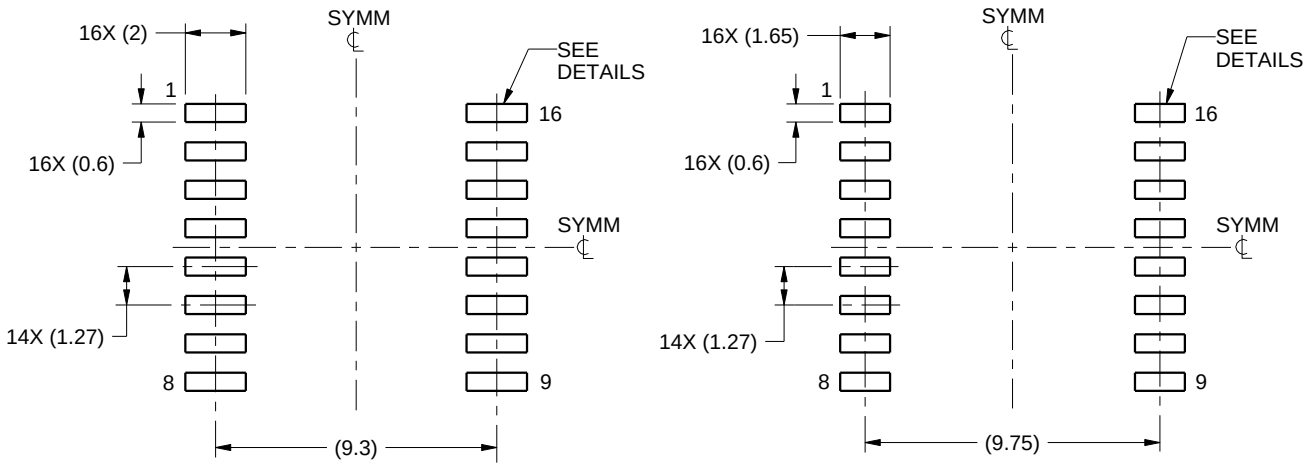
SOIC - 2.65 mm max height

SOIC



NOTES:

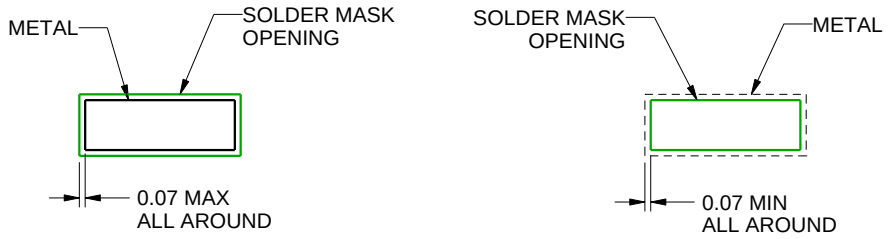
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.



IPC-7351 NOMINAL
7.3 mm CLEARANCE/CREEPAGE

HV / ISOLATION OPTION
8.1 mm CLEARANCE/CREEPAGE

LAND PATTERN EXAMPLE
SCALE:4X



NON SOLDER MASK DEFINED

SOLDER MASK DEFINED

SOLDER MASK DETAILS

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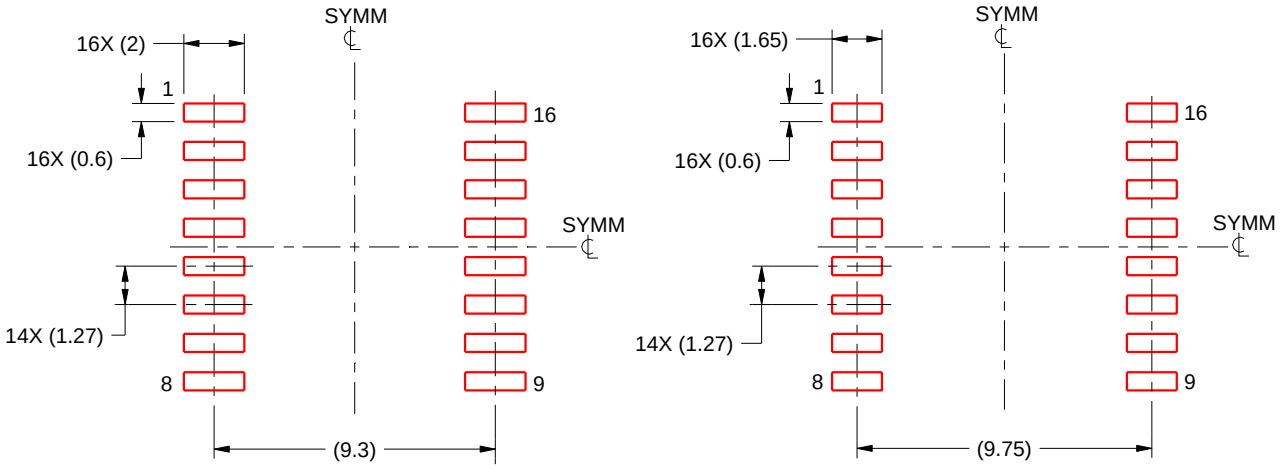
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



IPC-7351 NOMINAL
7.3 mm CLEARANCE/CREEPAGE

HV / ISOLATION OPTION
8.1 mm CLEARANCE/CREEPAGE

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:4X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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